FM25Q64

64M-BIT

Serial Flash Memory with 4KB Sectors, Dual and Quad I/O SPI

FIDELIX

Documents title

64M bit Serial Flash Memory with 4KB Sectors, Dual and Quad I/O SPI

Revision History

Revision No.	History	Draft date	Remark
0.0	Initial Draft	Jul.2010	preliminary
0.1	Write Status Register (01h) previous bits => cleared to 0 Change Read instructions tSHSL20ns => 10ns Change	Aug.18.2010	preliminary

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1. GENERAL DESCRIPTION

The FM25Q64 Serial Flash memory provides a storage solution for systems with limited space, pins and power. The 25Q series offers flexibility and performance well beyond ordinary Serial Flash devices. They are ideal for code shadowing to RAM, executing code directly from Dual/Quad SPI (XIP) and storing voice, text and data. The devices operate on a single 2.7V to 3.6V power supply with current consumption as low as 5mA active and 1μA for power-down. All devices offered in space-saving packages.

The FM25Q64 array is organized into 32.786 programmable pages of 256-bytes each. Up to 256 bytes can be programmed at a time using the Page Program instructions. Pages can be erased in groups of 16 (4KB sector erase) groups of 128 (32KB block erase), groups of 256 (64KB block erase) or the entire chip (chip erase). The FM25Q64 has 2,048 erasable sectors and 128 erasable blocks respectively. The small 4KB sectors allow for greater flexibility in applications that require data and parameter storage.

The FM25Q64 supports the standard Serial peripheral Interface (SPI), and a high performance Dual output as well as Dual I/O SPI using pins: Serial Clock, Chip Select, Serial Data I/O0(DI), Serial Data I/O1(DO). SPI clock frequencies of up to 104MHz are supported allowing equivalent clock rates of 208MHz for Dual Output and 416Mhz for Quad Output when using the Fast Read Dual/Quad Output instructions. These transfer rates are comparable to those of 8 and 16-bit Parallel Flash memories.

A Hold pin, Write protect pin and programmable write protection, with top or bottom array control, provide further control flexibility. Additionally, the device supports JEDEC standard manufacturer and device identification with a 4K-bit Secured OTP.

2. FEATURES

- **SpiFlash Memory**
  - FM25Q64: 64M-bit / 8M–byte
  - 256-bytes per programmable page
  - 4K-bit secured OTP
- **Standard, Dual or Quad SPI**
  - standard SPI: CLK, /CS, DI, DO, /WP, /Hold
  - Dual SPI: CLK, /CS, IO_0, IO_1, /WP, /Hold
  - Quad SPI: CLK, /CS, IO_0, IO_1, IO_2, IO_3
- **Highest Performance Serial Flash**
  - Up to 7X that of ordinary Serial Flash
  - 104MHz clock operation
  - 208MHz equivalent Dual SPI
  - 416MHz equivalent Quad SPI
  - 50MB/S continuous data transfer rate
  - 31MB/S random access (32-byte fetch)
  - Comparable to X16 Parallel Flash
- **Package Material**
  - Fidelix all product Green package
    Lead-free
    RoHS Compliant
    Halogen-free

- **Advanced Security Features**
  - Software and Hardware Write-protect
  - Top or Bottom, Sector or Block selection
  - Lock-Down and OTP protection
- **Flexible Architecture with 4KB sectors**
  - Uniform Sector Erase (4K-byte)
  - Uniform Block Erase (32K and 64K-bytes)
  - program one to 256 bytes
  - Up to 100,000 erase/write cycles
  - 20-years data retention
  - Erase/Program Suspend & Resume
- **Low Power, wide Temperature Range**
  - Single 2.7 to 3.6V supply
  - 5mA active current, <1μA Power-down (typ.)
  - -40℃ to +85℃ operating range
- **Space Efficient Packaging**
  - 8-pin SOIC 208mil
  - 16-pin SOIC 300-mil
  - 8-pin DIP 300mil
  - 8-pad WSON 6x5-mm

3. PIN CONFIGURATION SOIC 208-MIL

/CS	1	8	VCC
DO(IO1)	2	7	/HOLD(IO3)
/WP(IO2)	3	6	CLK
GND	4	5	DI(IO0)
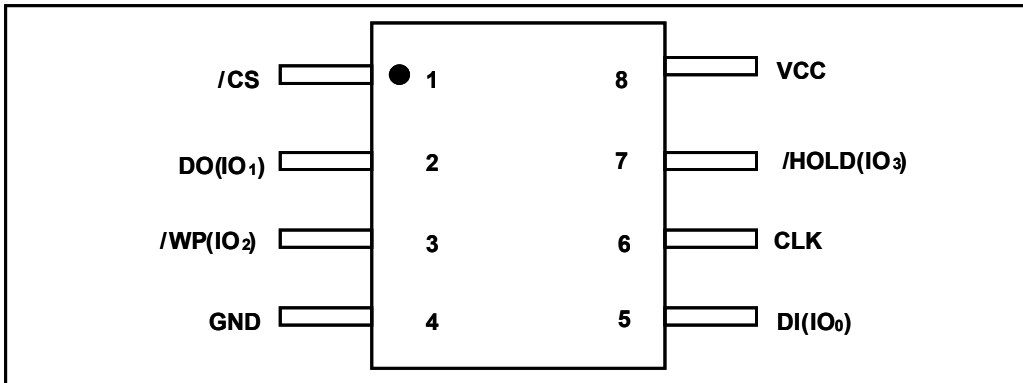
Figure 1a. pin Assignments, 8-pin SOIC 208-mil

4. PAD CONFIGURATION WSON 6X5-MM

/CS	1	8	VCC
DO(IO1)	2	7	/HOLD(IO3)
/WP(IO2)	3	6	CLK
GND	4	5	DI(IO0)
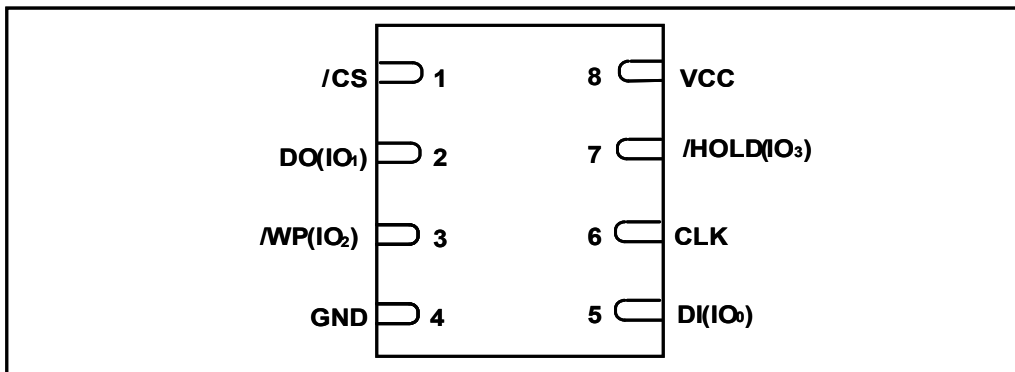
Figure 1b. Pad Assignments, 8-pad WSON

5. PIN CONFIGURATION 8-Pin PDIP 300-Mil

/CS			VCC
DO(IO1)			/HOLD(IO3)
/WP(IO2)			CLK
GND			DI(IO0)
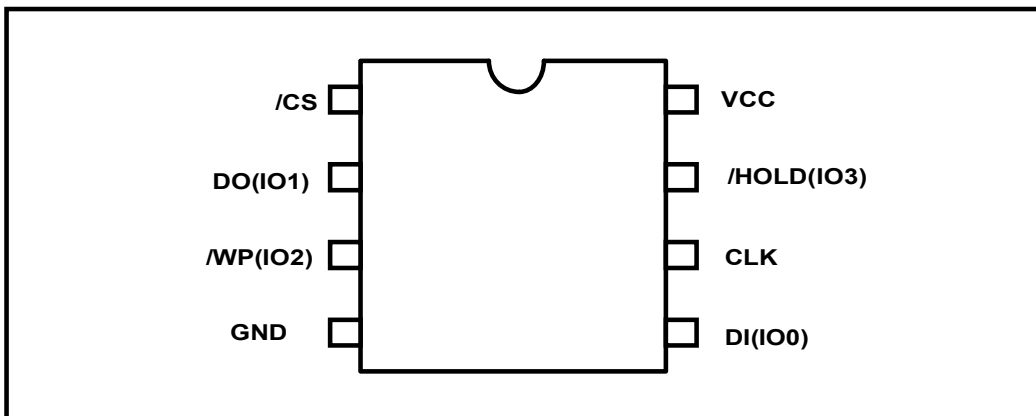
Figure 1c. Assignments, 8-pin PDIP 300-mil

6. PIN DESCRIPTION SOIC 208-MIL, PDIP 300MIL AND WSON 6X5MM

PIN NO.	PIN NAME	I/O	FUCTION
1	/CS	I	Chip Select Input
2	DO(IO1)	I/O	Data Output (Data Input Output 1)*1
3	/WP(IO2)	I/O	Write Protect Input (Data Input output) *2
4	GND		Ground
5	DI(IO0)	I/O	Data Input (Data Input Output 0)*1
6	CLK	I	Serial Clock Input
7	/HOLD(IO3)	I/O	Hold Input (Data Input output 3) *2
8	VCC		Power Supply

*1 IO0 and IO1 are used for Dual and Quad instructions
*2 IO0－IO3 are used for Quad instructions

7. PIN CONFIGURATION SOIC 300-MIL

/HOLD(IO$_3$)	1		16	CLK
VCC	2		15	DI(IO$_0$)
N/C	3		14	N/C
N/C	4		13	N/C
N/C	5		12	N/C
N/C	6		11	N/C
/CS	7		10	GND
DO(IO$_1$)	8		9	/WP(IO$_2$)
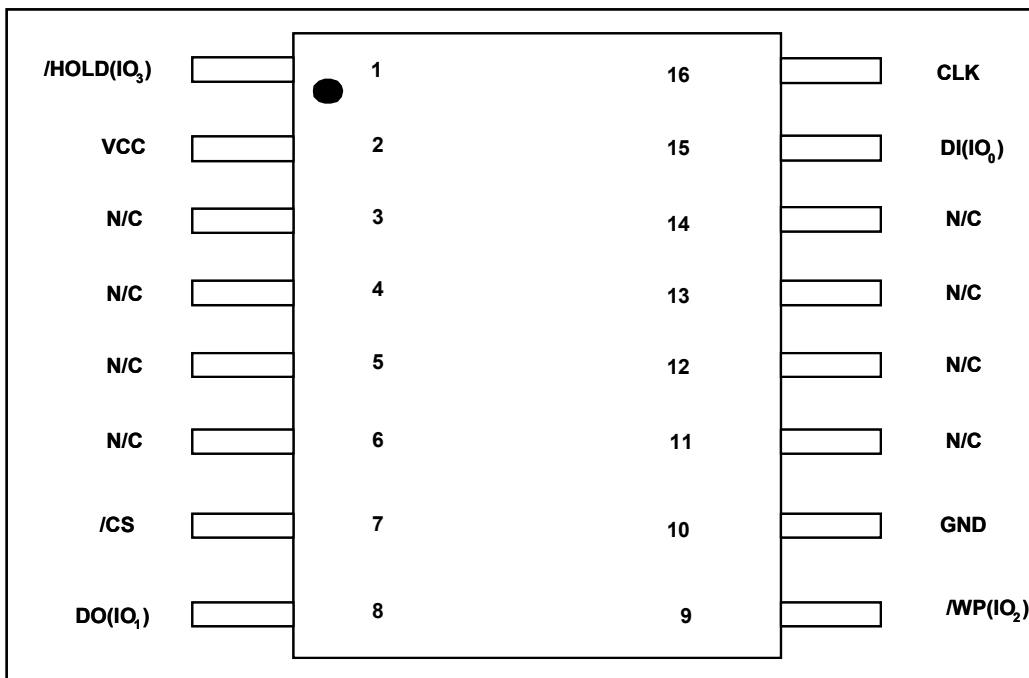
Figure 1d. Pin Assignments, 16-pin SOIC 300-mil

8. PIN DESCRIPTION SOIC 300-MIL

PAD NO.	PAD NAME	I/O	FUCTION
1	/HOLD(IO3)	I/O	Hold Input(Data Input Output 3)* ²
2	VCC		Power Supply
3	N/C		No Connect
4	N/C		No Connect
5	N/C		No Connect
6	N/C		No Connect
7	/CS	I	Chip Select Input
8	DO(IO1)	I/O	Data output (Data Input Output 1)* ¹
9	/WP(IO2)	I/O	Write Protection Input (Data Input Output 2)* ²
10	GND		Ground
11	N/C		No Connect
12	N/C		No Connect
13	N/C		No Connect
14	N/C		No Connect
15	DI(IO0)	I/O	Data Input (Data Input Output 0)* ¹
16	CLK	I	Serial Clock Input

*1 IO0 and IO1 are used for Dual and Quad instructions
*2 IO0_IO3 are used for Quad instructions

8.1 Package Types

8-pin plastic 208-mil width SOIC, 6x5-mm WSON, 8-pin PDIP and 16-pin plastic 300-mil width SOIC as shown in figure 1a, 1b,1c and 1d respectively.

Package diagrams and dimensions are illustrated at the end of this datasheet.

8.2 Chip Select (/CS)

The SPI Chip Select (/CS) pin enables and disables device operation. When /CS is high the device is deselected and the Serial Data Output (DO, or IO0, IO1, IO2, IO3) pins are at high impedance. When deselected, the device power consumption will be at standby levels unless an internal erase, program or write status register cycle is in progress. When /CS is brought low the device will be selected, power consumption will increase to active levels and instructions can be written to and read data from the device. After power-up, /CS must transition from high to low before a new instruction will be accepted. The /CS input must track the VCC supply level at power-up (see "Write Protection" and figure 30). If needed a pull-up resister on /CS can be used to accomplish this.

8.3 Serial Data Input, Output and IOs (DI, DO and IO0, IO1, IO2, IO3)

The FM25Q64 supports standard SPI, Dual SPI and Quad SPI operation. Standard SPI instructions use the unidirectional DI (input) pin to serially write instructions, addresses or data to the device on the rising edge of the Serial Clock (CLK) input pin. Standard SPI also uses the unidirectional DO (output) to read data or status from the device on the falling edge of CLK.

Dual and Quad SPI instructions use the bidirectional IO pins to serially write instructions, addresses or data to the device on the rising edge of CLK and read data or status from the device on the falling edge of CLK. Quad SPI instructions require the non-volatile Quad Enable bit (QE) in Status Register-2 to be set. When QE=1 the /WP pin becomes IO2 and /HOLD pin becomes IO3.

8.4 Write Protect (/WP)

The Write Protect (/WP) pin can be used to prevent the Status Register from being written. Used in conjunction with the Status Register's Block Protect (SEC. TB. BP2, Bp1 and BP0) bits and Status Register Protect (SRP) bits, a portion or the entire memory array can be hardware protected. The /WP pin is active low. When the QE bit of Status Register-2 is set for Quad I/O, the /WP pin (Hardware Write Protect) function is not available since this pin is used for IO2. See figure 1a, 1b, 1c and 1d for the pin configuration of Quad I/O operation.

8.5 HOLD (/HOLD)

The /HOLD pin allows the device to be paused while it is actively selected. When /HOLD is brought low, while /CS is low, the DO pin will be at high impedance and signals on the DI and CLK pins will be ignored (don't care). When /HOLD is brought high, device operation can resume. The /HOLD function cab be useful when multiple devices are sharing the same SPI signals. The /HOLD pin is active low. When the QE bit of Status Register-2 is set Quad I/O, the /HOLD pin function is not available since this pin used for IO3. See figure 1a, 1b, 1c and 1d for the pin configuration of Quad I/O operation.

8.6 Serial Clock (CLK)
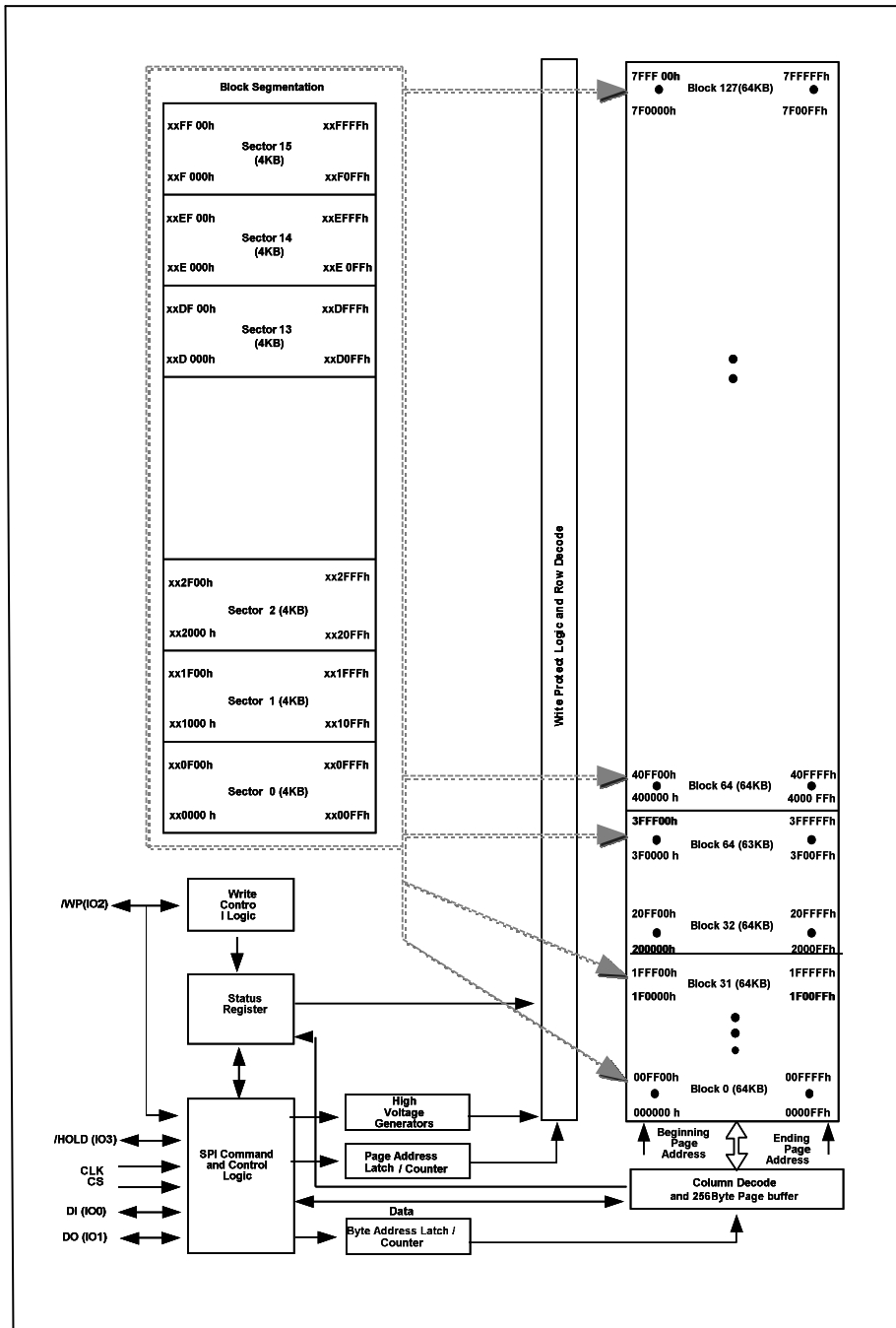
The SPI Serial Clock Input (CLK) pin provides the timing for serial input and output operations. ("See SPI Operations")

9. BLOCK DIAGRAM

10. FUNCTIONAL DESCRIPTION

10.1 SPI OPERATIONS

10.1.1 Standard SPI Instructions
The FM25Q64 is accessed through an SPI compatible bus consisting of four signals: Serial Clock (CLK). Chip Select (/CS), Serial Data Input (DI) and Serial Data Output (DO). Standard SPI instructions use the DI input pin to serially write instructions, addresses or data to the device on the rising edge of CLK. The DO output pin is used to read data or status from the device on the falling edge of CLK.

SPI bus operation Modes 0 (0, 0) and 3 (1, 1) are supported. The primary difference between Mode 0 and Mode 3 concerns the normal state of the CLK signal when the SPI bus master is in standby and data is not being transferred to the Serial Flash. For Mode 0 the CLK signal is normally low on the falling and rising edges of /CS. For Mode 3 the CLK signal is normally high on the falling and rising edges of /CS.

10.1.2 Dual SPI Instructions
The FM25Q64 supports Dual SPI operation when using the "Fast Read Dual I/O" (BB hex) instruction. This instruction allows data to be transferred to or from the device at three to four the rate ordinary Serial Flash devices. The Dual Read instruction is ideal for quickly downloading code to RAM upon power-up (code-shadowing) or for executing non-speed-critical code directly from the SPI bus (XIP). When using Dual SPI instructions the DI and DO pins become bidirectional I/0 pins; IO0 and IO1.

10.1.3 Quad SPI Instructions
The FM25Q64 supports Quad SPI operation when using the "Fast Read Quad I/O" (EB hex). This instruction allows data to be transferred to or from the device six to seven times the rate of ordinary Serial Flash. The Quad Read instruction offers a significant improvement in continuous and random access transfer rates allowing fast code-shadowing to RAM or execution directly from the SPI bus (XIP). When using Quad SPI instruction the DI and DO pins become bidirectional IO0 and IO1, and the /WP and /HOLD pins become IO2 and IO3 respectively. Quad SPI instructions require the non-volatile Quad Enable bit (QE) in Status Register-2 to be set.

10.1.4 Hold Function
The /HOLD pin is used to pause a serial sequence of the SPI flash memory without resetting the clocking sequence. To activate the /HOLD mode, the /CS must be in active low state. The /HOLD mode begins when the CLK in active low state coincides with the falling edge of the /HOLD signal. The HOLD mode ends when the /HOLD signal's rising edge coincides with the CLK in active low state.
If the falling edge of the /HOLD signal does not coincide with the CLK in active low state, then the device enters HOLD mode when the CLK reaches the next active low state. Similarly, if the rising edge of the /HOLD signal does not coincide with the CLK in active low state, then the device exits in HOLD mode when the CLK reaches the next active low state. See Figure.2 for HOLD condition waveform.
If /CS is driven active high during a HOLD condition, it resets the internal logic of the device. As long as /HOLD signal is low, the memory remains in the HOLD condition. To resume communication with the device, /HOLD must be driven active high, and /CS must be driven active low. See 12.11 for HOLD timing.
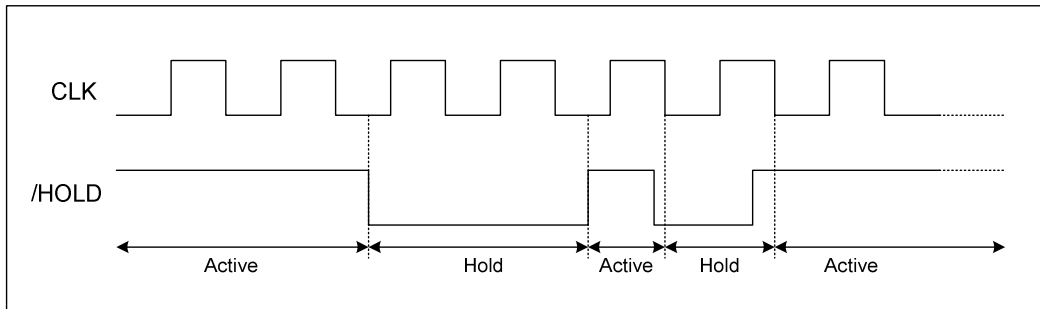
Figure2. Hold condition waveform

10.2 WRITE PROTECTION

Applications that use non-volatile memory must take consideration the possibility of noise and other adverse system conditions that may compromise data integrity. To address this concern the FM25Q64 provides several means to protect data from inadvertent writes.

10.2.1 Write protect Features

● Device resets when VCC is below threshold

● Time delay write disable after Power-up

● Write enable/disable instructions and automatic write disable after program and erase

● Software and Hardware (/WP pin) write protection using Status Register

● Write Protection using Power-down instruction

● Lock Down write protection until next power-up

● One Time Program (OTP) write protection

Upon power-up at power down the FM25Q64 will maintain a reset condition while VCC is below the threshold value of VWI, (See Power-up Timing and Voltage Levels and Figure 30). While reset, all operations are disabled and no instruction is recognized. During power-up and after the VCC voltage exceeds VWI, instructions related with all program and erase are further disabled for a time delay of tPUW. This includes the write Enable, Page program, Sector Erase, Block Erase, Chip Erase, Write Security Register and the Write Status Register instructions. Note that the chip select pin (/CS) must track the VCC supply level at power-up until the VCC-min level and tVSL time delay is reached. If needed a pull-up resister on /CS can be used to accomplish this.

After power-up the device is automatically placed in a write-disabled state with Status Register Write Enable Latch (WEL) set to a 0. A Write Enable instruction must be issued before a Page program, Sector Erase Chip Erase or Write Status Register and then instructions will be accepted. After completing a program, erase or write instruction the write Enable (WEL) is automatically cleared to write-disabled state of 0.

Software controlled write protection is facilitated using the Write Status Register instruction and setting the Status Register protect (SRP) and Block protect (SEC, TB, BP2, BP1, and BP0) bits. These setting allow a portion or all the memory to be configured as read only. Used in conjunction with the Write Protect (/WP) pin, changes to the Status Register can be enabled or disabled under hardware control. See Status Register for further information. Additionally, the Power-down instruction offers an extra level of write protection as all instructions are ignored except for Release power-down instruction.

11. CONTROL AND STATUS REGISTER

The Read Status Register instruction can be used to provide status on the availability of the Flash memory array, if the device is write enabled or disabled, the state of write protection and the Quad SPI setting. The Write Status Register instruction can be used to configure the devices write protection features and Quad SPI setting. Write access to the Status Register is controlled by in some cases of the /WP pin.

11.1 STATUS REGISTER

11.1.1 BUSY

BUSY is a read only bit in the status register (S0) that is set to a 1 state when the device is executing a Page Program, Sector Erase, Block Erase, Chip Erase or Write Status Register instruction. During this time the device will ignore further instruction except for the Read Status Register and Erase Suspend instruction (see tW, tPP, tSE, tBE1, tBE2 and tCE in AC Characteristics). When the program, erase or write status register instruction has completed, the BUSY bit will be cleared to a 0 state indicating the device is ready for further instructions.

11.1.2 Write Enable Latch (WEL)

Write Enable Latch (WEL) is a read only bit in the status register (S1) that is set to a 1 after executing a Write Enable instruction. The WEL status bit is cleared to a 0, When device is write disabled. A write disable state occurs upon power-up or after any of the following instructions: Write Disable, Page Program, Sector Erase, Block Erase, Chip Erase and Write Status Register.

11.1.3 Block Protect Bits (BP2, BP1, BP0)

The Block Protect Bits (BP2, BP1, BP0) are non-volatile read/write bits in the status register (S4, S3, and S2) that provide write protection control and status. Block protect bits can be set using the Write Status Register Instruction (see tW in AC characteristics). All none or a portion of the memory array can be protected from Program and Erase instructions (see Status Register Memory Protection table). The factory default setting for the Block Protection Bits is 0, none of the array protected.

11.1.4 Top/Bottom Block protect (TB)

The non-volatile Top/Bottom bit (TB) controls if the Block Protect Bits (BP2, BP1, BP0) protect from the Top (TB=0) or the Bottom (TB=1) of the array as shown in the Status Register Memory Protection table. The factory default setting is TB=0. The TB bit can be set with the Write Status Register Instruction depending on the state of the SRP0, SRP1 and WEL bits.

11.1.5 Sector/Block Protect (SEC)

The non-volatile Sector protect bit (SEC) controls if the Block Protect Bits (BP2, BP1, BP0) protect 4KB Sectors (SEC=1)or 64KB Blocks (SEC=0) in the Top (TB=0) or the Bottom (TB=1) of the array as shown in the Status Register Memory protection table. The default setting is SEC=0.

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11.1.6 Status Register protect (SRP1, SRP0)

The Status Register Protect bits (SRP1 and SRP0) are non-volatile read/write bits in the status register (S8 and S7). The SRP bits control the method of write protection: software protection, hardware protection, power supply lock-down or one time programmable (OTP) protection.

SRP1	SRP0	/WP	Status Register	Description
0	0	X	Software Protection	/WP pin no control. The register can be written to after a Write Enable instruction, WEL=1. [Factory Default]
0	1	0	Hardware Protected	When /WP pin is low the Status Register locked and can not be written to.
0	1	1	Hardware Unprotected	When /WP pin is high the Status register is unlocked and can be written to after a Write Enable instruction, WEL=1
1	0	X	Power Supply Lock-Down	Status Register is protected and can not be written to again until the next power-down, power-up cycle[1].
1	1	X	One Time Program	Status Register is permanently protected and can not be written to.

Note:
1. When SRP1, SRP0=(1,0), a power-down, power-up cycle will change SRP1, SRP0 to(0,0) state.

11.1.7 Erase/Program Suspend Status (SUS)

The Suspend Status bit is a read only bit in the status register (S15) that is set to 1 after executing an Erase/Program Suspend (75h) instruction. The SUS status bit is cleared to 0 by Erase/Program Resume (7Ah) instruction as well as a power-down, power-up cycle.

11.1.8 Quad Enable (QE)

The Quad Enable (QE) bit is a non-volatile read/write bit in the status register (S9) that allows Quad operation. When the QE bit is set to a 0 state (factory default) the /WP pin and /Hold are enabled. When the QE pin is set to a 1 the Quad IO2 and IO3 pins are enabled.

WARNING : The QE bit should never be set to a 1 during standard SPI or Dual SPI operation if the /WP or /HOLD pins are tied directly to the power supply or ground.

S7	S6	S5	S4	S3	S2	S1	S0
SRP0	SEC	TB	BP2	BP1	BP0	WEL	BUSY

STATUS REGISTER PROTECT
(NON-VOLATILE)

SECTOR PROTECT
(NON-VOLATILE)

TOP/BOTTOM WRITE PROTECT
(NON-VOLATILE)

BLOCK PROTECT BITS
(NON-VOLATILE)

WRITE ENABLE LATCH

ERASE OR WRITE IN PROGRESS
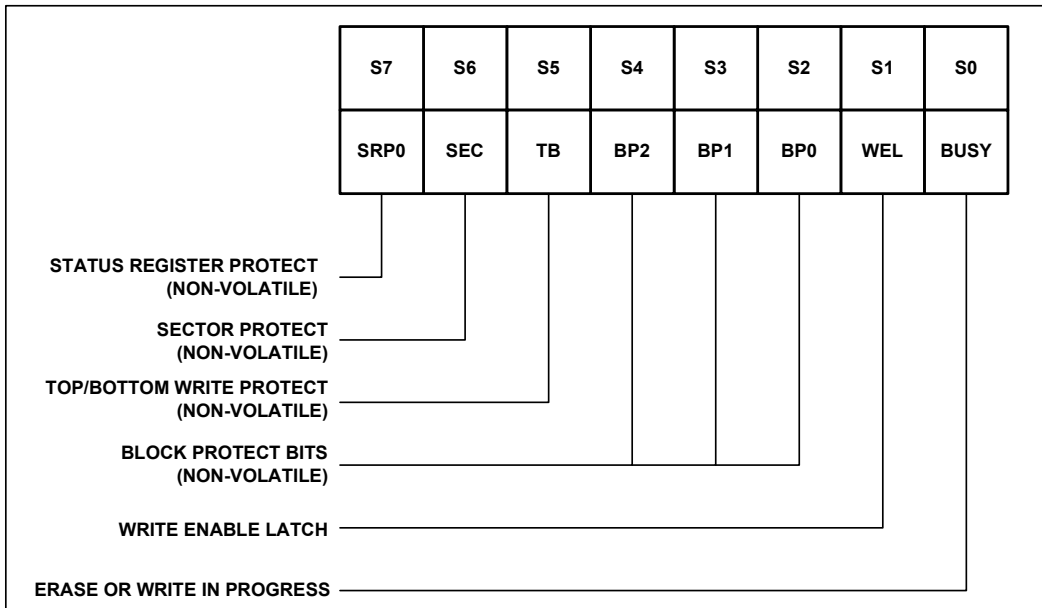
Figure 3a. Status Register-1

S15	S14	S13	S12	S11	S10	S9	S8
SUS	(R)	(R)	(R)	(R)	(R)	QE	SRP1

SUSPEND STATUS

RESERVED

QUAD ENABLE
(NON-VOLATILE)

STATUS REGISTER PROTECT1
(NON-VOLATILE)
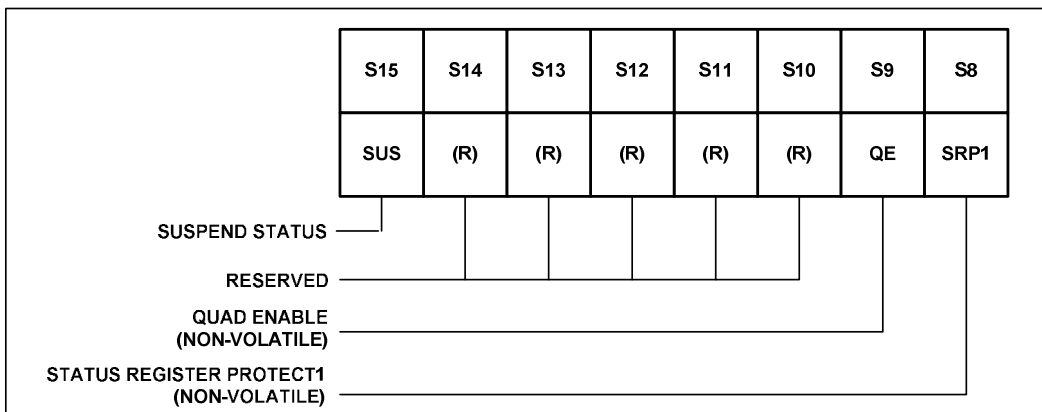
Figure 3b. Status Register-2

11.1.9 Status Register Memory Protection

STATUS REGISTER[1]					MEMORY PROTECTION			
SEC	TB	BP2	BP1	BP0	BLOCK(S)	ADDRESSES	DENSITY	PORTION
X	X	0	0	0	NONE	NONE	NONE	NONE
0	0	0	0	1	126 and 127	7E0000h-7FFFFFh	128KB	Upper 1/64
0	0	0	1	0	124 thru 127	7C0000h-7FFFFFh	256KB	Upper 1/32
0	0	0	1	1	120 thru 127	780000h-7FFFFFh	512KB	Upper 1/16
0	0	1	0	0	112 thru 127	700000h-7FFFFFh	1M	Upper 1/8
0	0	1	0	1	96 thru 127	600000h-7FFFFFh	2MB	Upper 1/4
0	0	1	1	0	64 thru 127	400000h-7FFFFFh	4MB	Upper 1/2
0	1	0	0	1	0 and 1	000000h-01FFFFh	128KB	Lower 1/64
0	1	0	1	0	0 thru 3	000000h-03FFFFh	256KB	Lower 1/32
0	1	0	1	1	0 thru 7	000000h-07FFFFh	512KB	Lower 1/16
0	1	1	0	0	0 thru 15	000000h-0FFFFFh	1MB	Lower 1/8
0	1	1	0	1	0 thru 31	000000h-1FFFFFh	2MB	Lower 1/4
0	1	1	1	0	0 thru 63	000000h-3FFFFFh	4MB	Lower 1/2
X	X	1	1	1	0 thru 127	000000h-7FFFFFh	8MB	ALL
1	0	0	0	1	127	7FF000h-7FFFFFh	4KB	Top Block
1	0	0	1	0	127	7FE000h-7FFFFFh	8KB	Top Block
1	0	0	1	1	127	7FC000h-7FFFFFh	16KB	Top Block
1	0	1	0	X	127	7F8000h-7FFFFFh	32KB	Top Block
1	1	0	0	1	0	000000h-000FFFh	4KB	Bottom Block
1	1	0	1	0	0	000000h-001FFFh	8KB	Bottom Block
1	1	0	1	1	0	000000h-003FFFh	16KB	Bottom Block
1	1	1	0	X	0	000000h-007FFFh	32KB	Bottom Block

Note :
  1. X = don't care

11.2 INSTRUCTIONS

The instruction set of the FM25Q64 consists of fifteen basic instructions that are fully controlled through the SPI bus (see Instruction Set table). Instructions are initiated with the falling edge of Chip Select (/CS). The first byte of data clocked into the DI input provides the instruction code. Data on the DI input is sampled on the rising edge of clock with most significant bit (MSB) first.

Instructions vary in length from a single byte to several bytes and may be followed by address bytes, data bytes, dummy bytes (don't care), and in some cases, a combination. Instructions are completed with the rising edge of edge /CS. Clock relative timing diagrams for each instruction are included in figures 4 through 29. All read instructions can be completed after any clocked bit. However, all instructions that Write, Program or Erase must complete on a byte (/CS driven high after a full 8-bit have been clocked) otherwise the instruction will be terminated. This feature further protects the device from inadvertent writes. Additionally, while the memory is being programmed or erased, or when the Status Register is being written, all instructions except for Read Register will be ignored until the program or erase cycle has completed.

11.2.1 Manufacturer and Device Identification

MANUFACTRER ID	(M7-M0)	
Fidelix Semiconductor	F8h	
Device ID	(ID7-ID0)	(ID15-ID0)
Instruction	ABh, 90h	9Fh
FM25Q64	16h	3217h

11.2.2 Instruction Set Table 1[1]

INSTRUCTION NAME	BYTE 1 (CODE)	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
Write Enable	06h					
Write Enable for Volatile Status Register	50h					
Write Disable	04h					
Read Status Register-1	05h	(S7-S0) [2]				
Read Status Register-2	35h	(S15-S8)[2]				
Write Status Register	01h	(S7-S0)	(S15-S8)			
Page Program	02h	A23-A16	A15-A8	A7-A0	(D7-D0)	
Quad Data Input Page Program[3]	32h	A23-A16	A15-A8	A7-A0	(D7-D0, …)³	
Quad Page Program	38h	A23-A0, (D7-D0)	A15-A8	A7-A0	(D7-D0, …)³	
Block Erase (64KB)	D8h	A23-A16	A15-A8	A7-A0		
Block Erase (32KB)	52h	A23-A16	A15-A8	A7-A0		
Sector Erase (4KB)	20h	A23-A16	A15-A8	A7-A0		
Chip Erase	C7h/60h					
Erase Suspend	75h					
Erase Resume	7Ah					
Power-down	B9h					
Mode Bit Reset[4]	FFh					
Release power down/ Device ID	ABh	dummy	dummy	dummy	(ID7-ID0) [5]	
Read Manufacturer/ Device ID[6]	90h	dummy	dummy	00h or 01h	(M7-M0)	(ID7-ID0)
Read Dual Manufacturer/ Device ID[6]	EFh	dummy	dummy	00h or 01h	(M7-M0) (ID7-ID0)	
Read Quad Manufacturer/ Device ID[6]	DFh	dummy	dummy	00h or 01h	(M7-M0…) (ID7-ID0…)	
Write Security Register	2Fh					
Read Security Register	2Bh	(S7-S0)				
Enter Secured OTP	B1h					
Exit Secured OTP	C1h					
Read JEDEC ID	9Fh	(M7-M0) Manufacturer	(ID7-ID0) Memory Type	(ID7-ID0) Capacity		

Notes:

1. Data bytes are shifted with Most Significant Bit first. Byte fields with data in parenthesis "()" indicate data being read from the device on the IO pin.

2. The Status Register contents will repeat continuously until /CS terminates the instruction.
3. Quad Data Input Page Program Input Data

         IO0 = (D4, D0 …)
         IO1 = (D5, D1 …)
         IO2 = (D6, D2 …)
         IO3 = (D7, D3 …)

4. This instruction is recommended when using the Dual or Quad Mode bit feature. See section 10.2.28 for more information.
5. The Device ID will repeat continuously until /CS terminates the instruction.
6. See Manufacturer and Device Identification table for Device ID information.

11.2.3 Instruction Set Table 2 (Read Instructions)

INSTRUCTION NAME	BYTE 1 (CODE)	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
Read Data	03h	A23-A16	A15-A8	A7-A0	(D7-D0)	
Fast Read Data	0Bh	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Fast Read Dual I/O	BBh	A23-A8[2]	A7-A0, M7-M0[2]	(D7-D0, …)[1]		
Fast Read Quad I/O	EBh	A23-A0, M7-M0[4]	(x,x,x,x, D7-D0,…)[5]	(D7-D0, …)[3]		
Set Burst with Wrap	77h	xxxxxx, W6-W4[4]				

Notes:

1: Dual Output data
         IO0 = (D6, D4, D2, D0)
         IO1 = (D7, D5, D3, D1)

2: Dual Input Address
         IO0 = A22, A20, A18, A16, A14, A12, A10, A8, A6, A4, A2, A0, M6, M4, M2, M0
         IO1 = A23, A21, A19, A17, A15, A13, A11, A9, A7, A5, A3, A1, M7, M5, M3, M1

3: Quad Output Data
         IO0 = (D4, D0…)
         IO1 = (D5, D1…)
         IO2 = (D6, D2…)
         IO3 = (D7, D3…)

4: Quad Input Address

IO0 = A20, A16, A12, A8,   A4, A0, M4, M0
IO1 = A21, A17, A13, A9,   A5, A1, M5, M1
IO2 = A22, A18, A14, A10,   A6, A2, M6, M2
IO3 = A23, A19, A15, A11,   A7, A3, M7, M3

Set Burst with Wrap Input
IO0 = x, x, x, x, x, x, W4,   x
IO1 = x, x, x, x, x, x, W5,   x
IO2 = x, x, x, x, x, x, W6,   x   ,
IO3 = x, x, x, x, x, x, x   x

5: Fast Read Quad I/O Data
         IO0 = (x, x, x, x, D4, D0…)
         IO1 = (x, x, x, x, D5, D1…)
         IO2 = (x, x, x, x, D6, D2…)
         IO3 = (x, x, x, x, D7, D3…)

11.2.4 Write Enable (06h)

The Write Enable instruction (Figure 4) sets the Write Enable Latch (WEL) bit in the Status Register to a 1. The WEL bit must be set prior to every Page Program, Sector Erase, Block Erase, Chip Erase and Write Status Register instruction. The Write Enable instruction is entered by driving /CS low, shifting the instruction code "06h" into Data Input (DI) pin on the rising edge of CLK, and then driving /CS high.
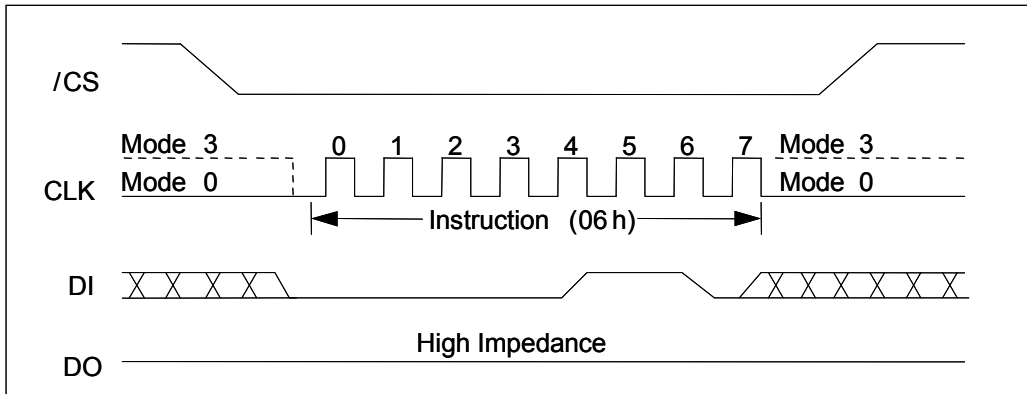

Figure 4. Write Enable Instruction Sequence Diagram

11.2.5 Write Enable for Volatile Status Register (50h)

The non-volatile Status Register bits described in section 12.1 can also be written to as volatile bits. This gives more flexibility to change the system configuration and memory protection schemes quickly without waiting for the typical non-volatile bit write cycles or affecting the endurance of the Status Register non-volatile bits. To write the volatile values into the Status Register bits, the Write Enable for Volatile Status Register (50h) instruction must be issued prior to a Write Status Register (01h) instruction. Write Enable for Volatile Status Register instruction (Figure 5) will not set the Write Enable Latch (WEL) bit, it is only valid for the Write Status Register instruction to change the volatile Status Register bit values
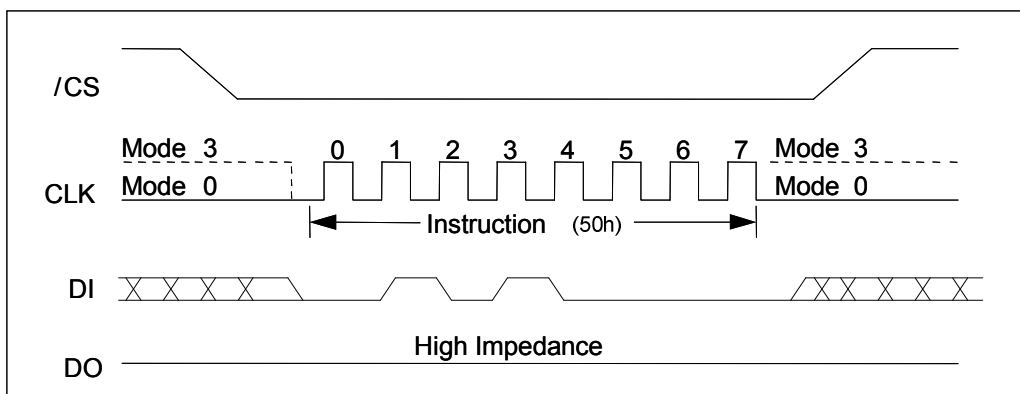

Figure 5. Write Enable for Volatile Status Register Instruction Sequence Diagram

11.2.6 Write Disable (04h)

The Write Disable instruction (Figure 6) resets the Write Enable Latch (WEL) bit in the Status Register to a 0. The Write Disable instruction in entered by driving /CS low, shifting the instruction code "04h" into the DI pin and then driving /CS high. Note that the WEL bit is automatically reset after Power-up and upon completion of the Write Status Register, Page Program, Sector Erase, Block Erase and Chip Erase instructions.   .
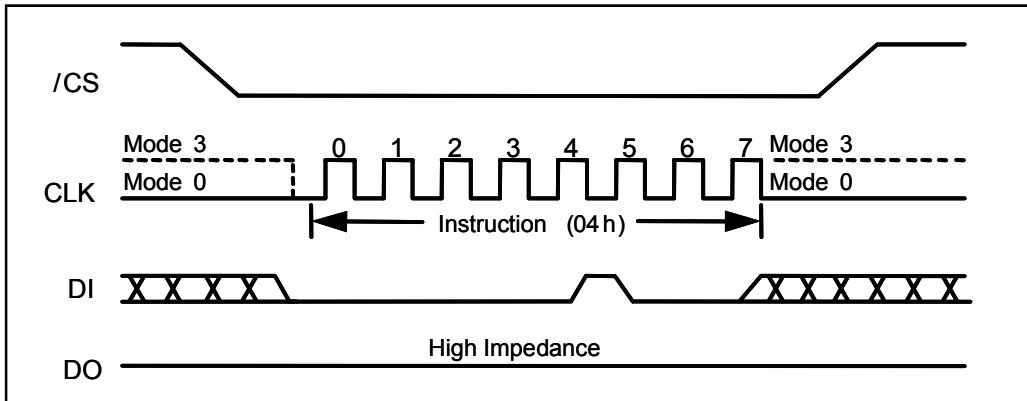

Figure 6. Write Disable Instruction Sequence Diagram

11.2.7 Read Status Register-1 (05h) and Read Status Register-2 (35h)

The Read Status Register instructions allow the 8-bit Status Register to be read, The instruction is entered by driving /CS low and shifting the instruction code "05h" for Status Register-1 and "35h" for Status Register-2 into the DI pin on the rising edge of CLK. The status register bits are then shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first as shown in figure 7. The Status Register bits are shown in figure 3a and 3b include the BUSY, WEL, BP2-BP0, TB, SEC, SRP0, SRP1 and QE bits (see description of the Status Register earlier in this datasheet).

The Status Register instruction may be used at any time, even while a Program, Erase, Write Security Register or Write Status Register cycle is in progress. This allows the BUSY status bit to be checked to determine when the cycle is complete and if the device can accept another instruction. The Status Register can be read continuously, as shown in Figure 7. The instruction is completed by driving /CS high.
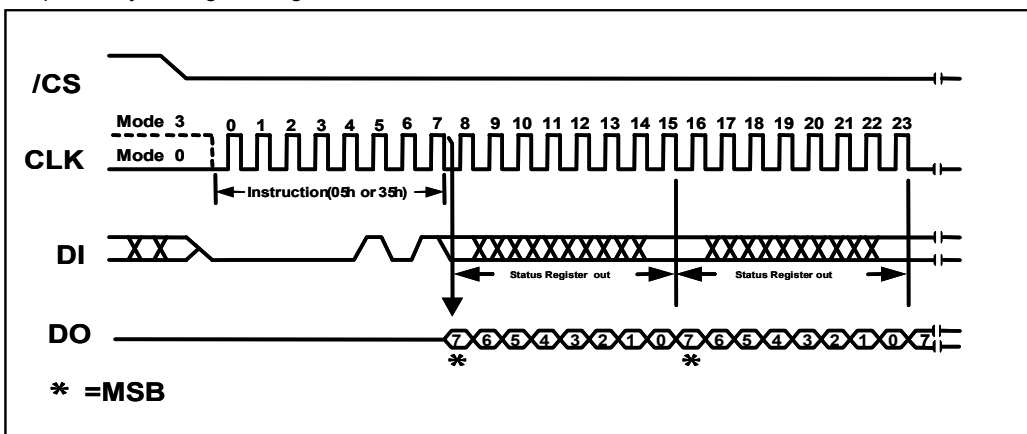

Figure 7. Read Status Register Instruction Sequence Diagram

11.2.8 Write Status Register (01h)

The Write Status Register instruction allows the Status Register to be written. A Write Enable instruction must previously have been executed for the device to accept the Write Status Register Instruction (Status Register bit WEL must equal 1). Once write is enabled, the instruction is entered by driving /CS low, sending the instruction code "01h", and then writing the status register data byte or word as illustrated in figure 8. The Status Register bits are shown in figure 3 and described earlier in this datasheet.

Only non-volatile Status Register bits SRP0, SEC, TB, BP2, BP1, BP0 (bits 7, 5, 4, 3, 2 of Status Register-1) and QE, SRP1 (bits 9 and 8 of Status Register-2) can be written to. All other Status Register bit locations are read-only and will not be affected by the Write Status Register instruction.

The /CS pin must be driven high after the eighth or sixteenth bit of data that is clocked in. If this is not done the Write Status Register instruction will not be executed. If /CS is driven high after the eighth clock, the QE and SRP1 bits will be cleared to 0. After /CS is driven high, the self-timed Write Status Register cycle will commence for a time duration of tw (See AC Characteristics). While the Write Status Register cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the BUSY bit. The BUSY bit is a 1 during the Write Status Register cycle and a 0 when the cycle is finished and ready to accept other instructions again. After the Write Status Register cycle has finished, The Write Enable Latch (WEL) bit in Status Register will be cleared to 0.

The Write Status Register instruction allows the Block Protect bits (SEC, TB, BP2, BP1 and BP0) to be set for protecting all, a portion, or none of the memory from erase and program instructions. Protected areas become read-only (see Status Register Memory Protection table and description). The Write Status Register instruction also allows the Status Register Protect bits (SRP0, SRP1) to be set. Those bits are used in conjunction with the Write protect (/WP) pin, Lock out or OTP features to disable writes to the status register. Please refer to 11.1.16 for detailed descriptions Status Register protection methods. Factory default all Status Register bits are 0.
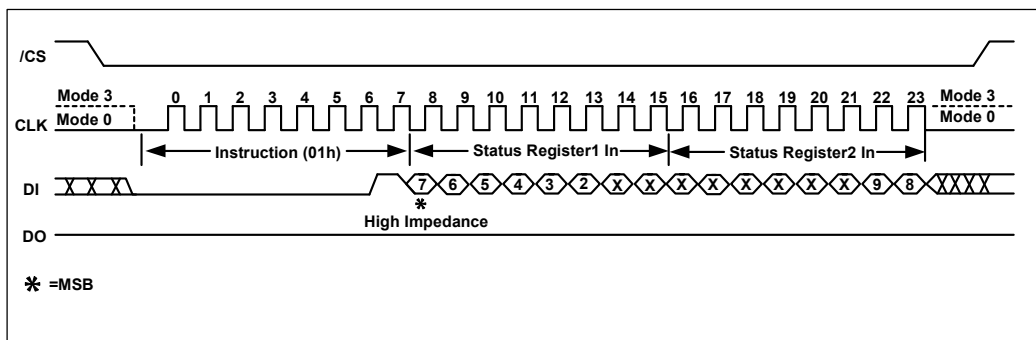

Figure 8. Write Status Register Instruction Sequence Diagram

11.2.9 Read Data (03h)

The Read Data instruction allows one more data bytes to be sequentially read from the memory. The instruction is initiated by driving the /CS pin low and then shifting the instruction code "03h" followed by a 24-bit address (A23-A0) into the DI pin. The code and address bits are latched on the rising edge of the CLK pin. After the address is received, the data byte of the addressed memory location

will be shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first. The address is automatically incremented to the next higher address after byte of data is shifted out allowing for a continuous stream of data. This means that the entire memory can be accessed with a single instruction as long as the clock continues. The instruction is completed by driving /CS high. The Read Data instruction sequence is shown in figure 9. If a Read Data instruction is issued while an Erase, Program or Write Status Register cycle is in process (BUSY=1) the instruction is ignored and will not have any effects on the current cycle. The Read Data instruction allows clock rates from D.C to a maximum of f_R (see AC Electrical Characteristics).
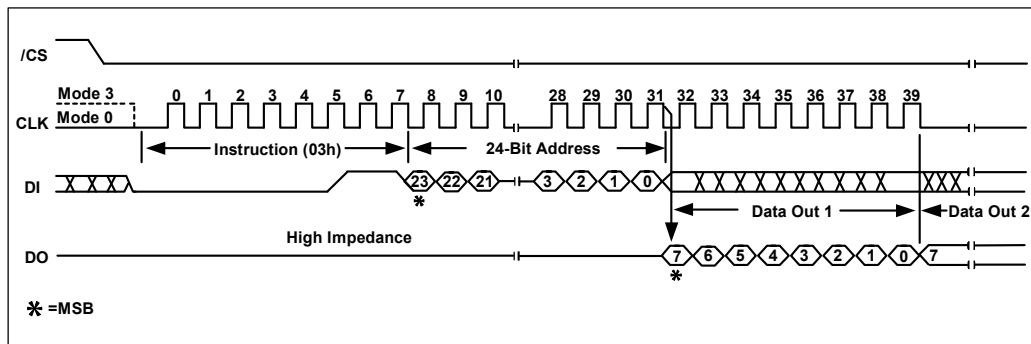
Figure 9. Read Data Register Instruction Sequence Diagram

11.2.10 Fast Read (0Bh)

The Fast Read instruction is similar to the Read Data instruction except that it can operate at the highest possible frequency of F_R (see AC Electrical Characteristics). This is accomplished by adding eight "dummy" clocks after the 24-bit address as shown in figure 10. The dummy clocks allow the device's internal circuits additional time for setting up the initial address. During the dummy clocks, The data value on the DO pin is a "don't care".
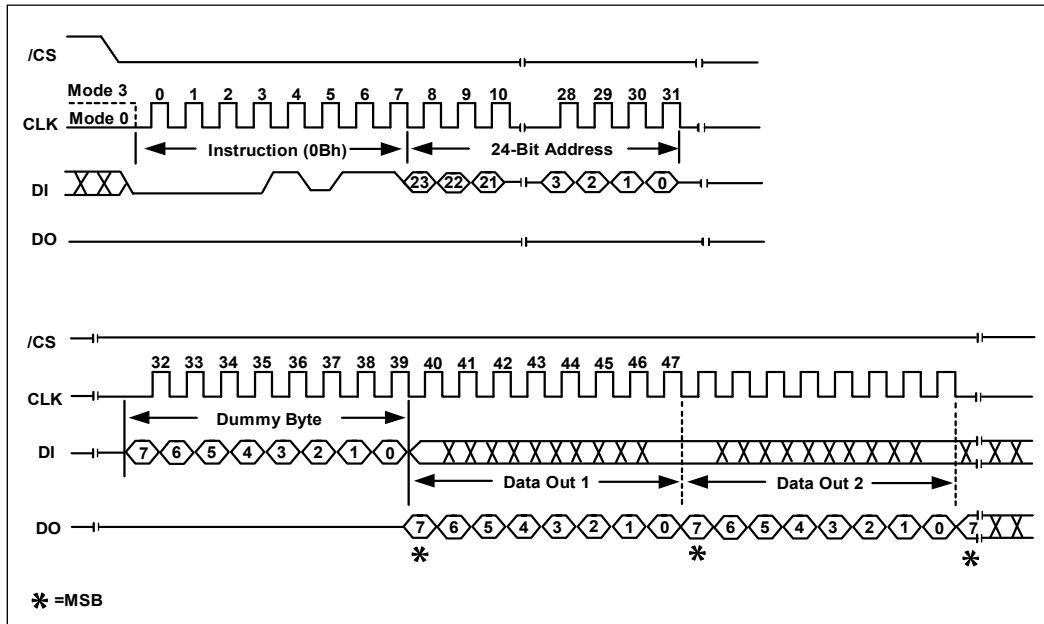

Figure 10. Fast Read Register Instruction Sequence Diagram

11.2.11 Fast Read Dual I/O (BBh)

The Fast Read Dual I/O (BBh) instruction allows for improved random access while maintaining two IO pins, IO_0 and IO_1. It is similar to the Fast Read Output (0Bh) instruction but with the capability to input the Address bits (A23-0) two bits and output data two bits per clock. This reduced instruction overhead may allow for code execution (XIP) directly from the Dual SPI in some applications.

The Fast Read Dual I/O instruction can further reduce instruction overhead through setting the Mode bits (M7-0) after the input Address bits (A23-0), as shown in figure 11a. The upper nibble of the Mode (M7-4) controls the length of the next Fast Read Dual I/O instruction through the instruction or exclusion of the first byte instruction code. The lower nibble bits of the Mode (M3-0) are don't care ("X"), However, the IO pins should be high-impedance prior to the falling edge of the first data out clock.

If the Mode bits (M7-0) equal "Ax" hex, then the next Fast Dual I/O instruction (after /CS is raised and then lowered) does not require the BBh instruction code, as shown in figure 11b. This reduces the instruction sequence by eight clocks and allows the address to be immediately entered after /CS is asserted low. If Mode bits (M7-0) are any value other "Ax" hex, the next instruction (after /CS is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. A Mode Bit Reset instruction can be used to reset Mode Bits (M7-0) before issuing normal instructions (See 11.2.25 for detailed descriptions).
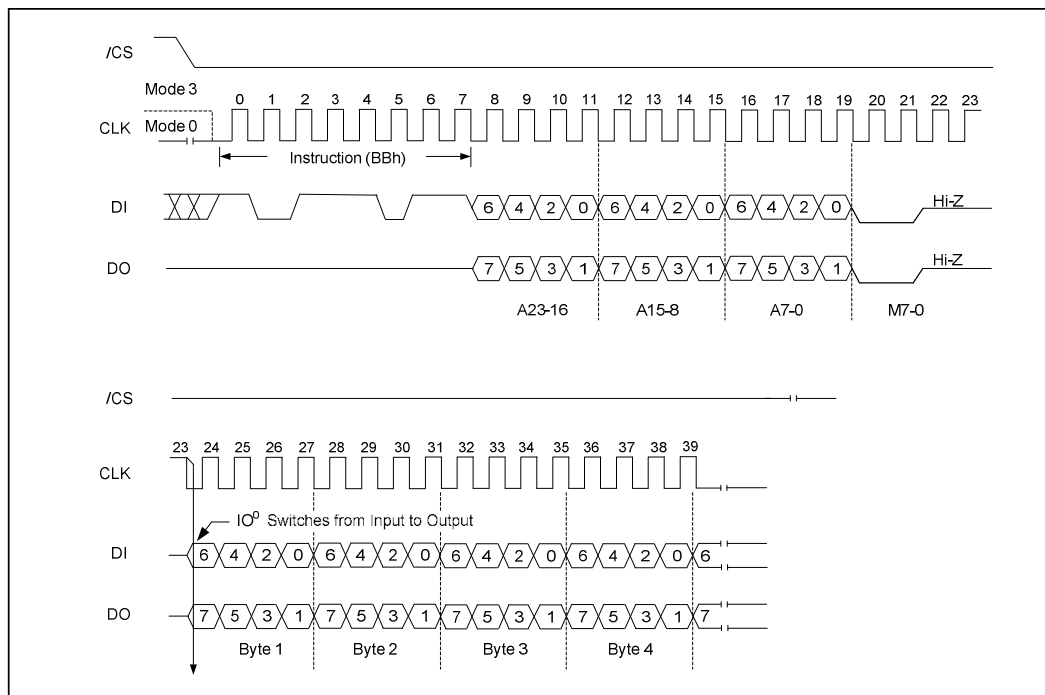

Figure 11a. Fast Read Dual Input/Output Instruction Sequence Diagram (M7-0 = 0xh or NOT Axh)

Figure 11b. Fast Read Dual Input/Output Instruction Sequence Diagram (M7-0 = Axh)

11.2.12 Fast Read Quad I/O (EBh)

The Fast Read Quad I/O (EBh) instruction is similar to the Fast Read Dual I/O (BBh) instruction except that address and data bits are input and output through four pins IO_0, IO_1, IO_2, and IO_3 and four Dummy clock are required prior to the data output. The Quad I/O dramatically reduces instruction overhead allowing faster random access for code executing (XIP) directly from the Quad SPI. The Quad Enable bit (QE) of Status Register-2 must be set to enable the Fast read Quad I/O Instruction.

The Fast Read Quad I/O instruction can further reduce instruction overhead through setting the Mode bits (M7-0) after the input Address bits (A23-0), as shown in figure 12a. The upper nibble of the Mode (M7-4) controls the length of the next Fast Read Quad I/O instruction through the instruction or exclusion of the first byte instruction code. The lower nibble bits of the Mode (M3-0) are don't care ("X"). However, the IO pins should be high-impedance prior to the falling edge of the first data out clock.

If the Mode bits (M7-0) equal "Ax" hex, then the next Fast Read Quad I/O instruction (after /CS is raised and then lowered) does not require the EBh instruction code, as shown in figure 12b. This reduces the instruction sequence by eight clocks allows the address to be immediately entered after /CS is asserted low. If the Mode bits (M7-0) are any value other than "Ax" hex, the next instruction (after /CS is raised and then lowered) requires the first byte instruction code, thus retuning normal operation. A Mode Bit Reset can be used to reset Mode Bits (M7-0) before issuing normal instructions (See 11.2.25 for detailed descriptions.)

Figure 12a. Fast Read Quad Input/Output Instruction Sequence Diagram (M7-0 = 0xh or NOT Axh)
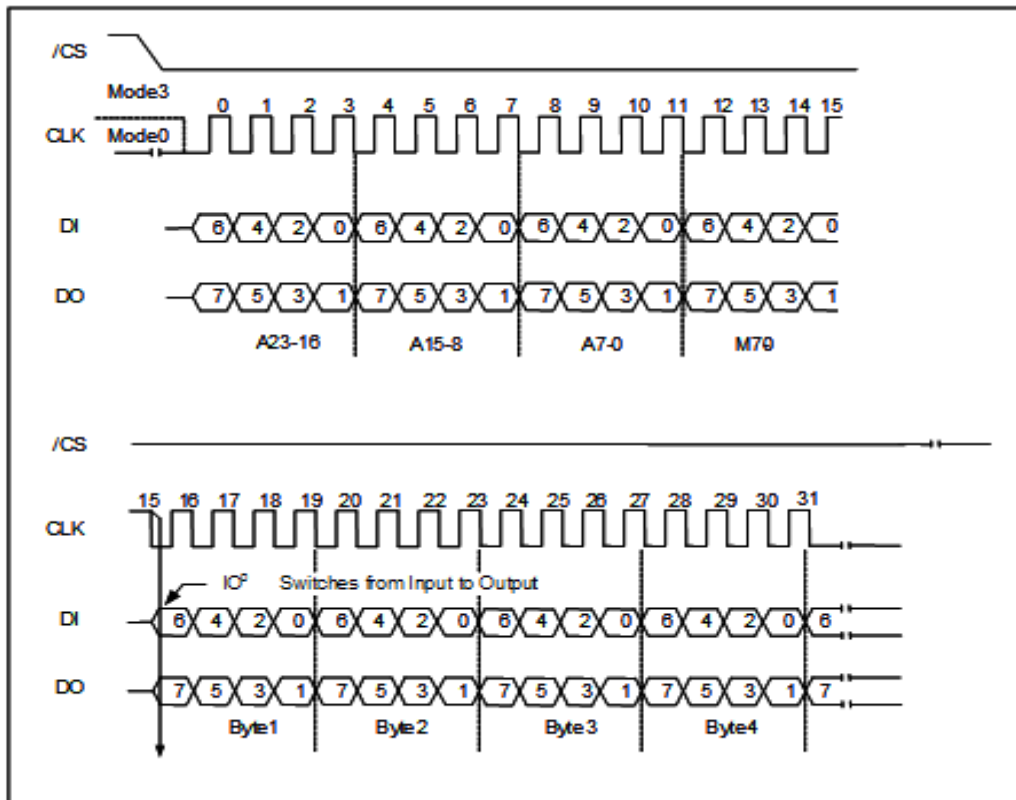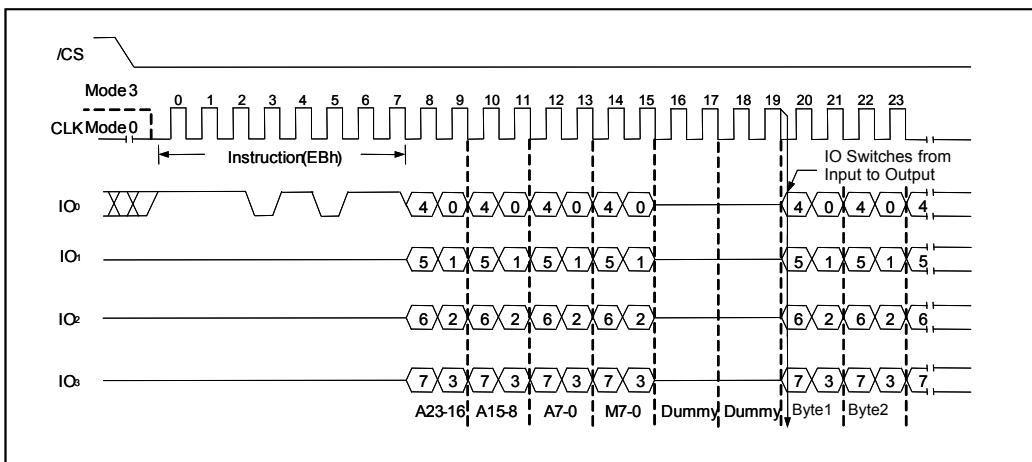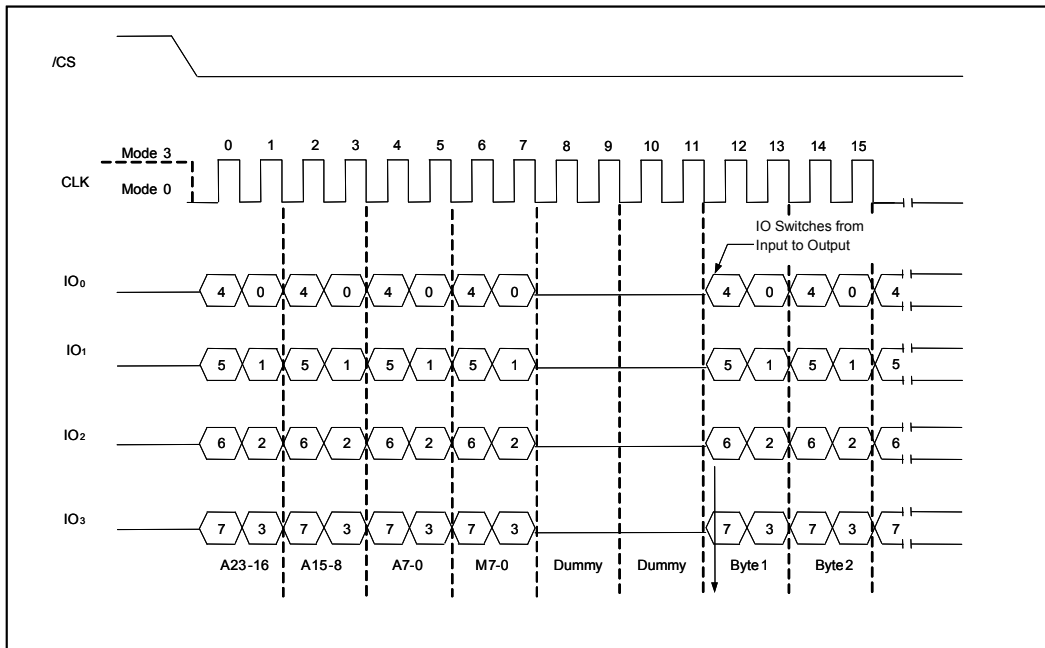
Figure 12b. Fast Read Quad Input/Output Instruction Sequence Diagram (M7-0 = Axh)

11.2.13 Page Program (02h)

The Page Program instruction allows from one byte to 256 bytes (a page) of data to be programmed at previously erased (FFh) memory locations. A Write Enable instruction must be executed before the device will accept the Page Program Instruction (Status Register bit WEL= 1). The instruction is initiated by driving the /CS pin low and then shifting the instruction code "02h" followed by a 24-bits address (A23-A0) and at least one data byte, into the DI pin. The /CS pin must be held low for the entire length of the instruction while data is being sent to the device. The Page Program instruction sequence is shown is figure 13.

If an entire 256 byte page is to be programmed, the last address byte (the 8 least significant address bits) should be set to 0. If the last address byte is not zero, and the number of clocks exceeds the remaining page length, the addressing will wrap to the beginning of the page. In some cases, less than 256 bytes (a partial page) can be programmed without having any effect on other bytes within the same page. One condition to perform a partial page program is that the number of clocks can not exceed the remaining page length. If more than 256 bytes are sent to the device the addressing will wrap to the beginning of the page and overwrite previously sent data.

As with the write and erase instructions, the /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Page Program instruction will not be executed. After /CS is driven high, the self-timed Page Program instruction will commence for a time duration of tPP (See AC Characteristics). While the Page Program cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Page Program cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Page Program cycle has finished and Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Page Program instruction will not be executed if the addressed page is protected by the Block Protect (SEC, TB, BP2, BP1, and BP0) bits,
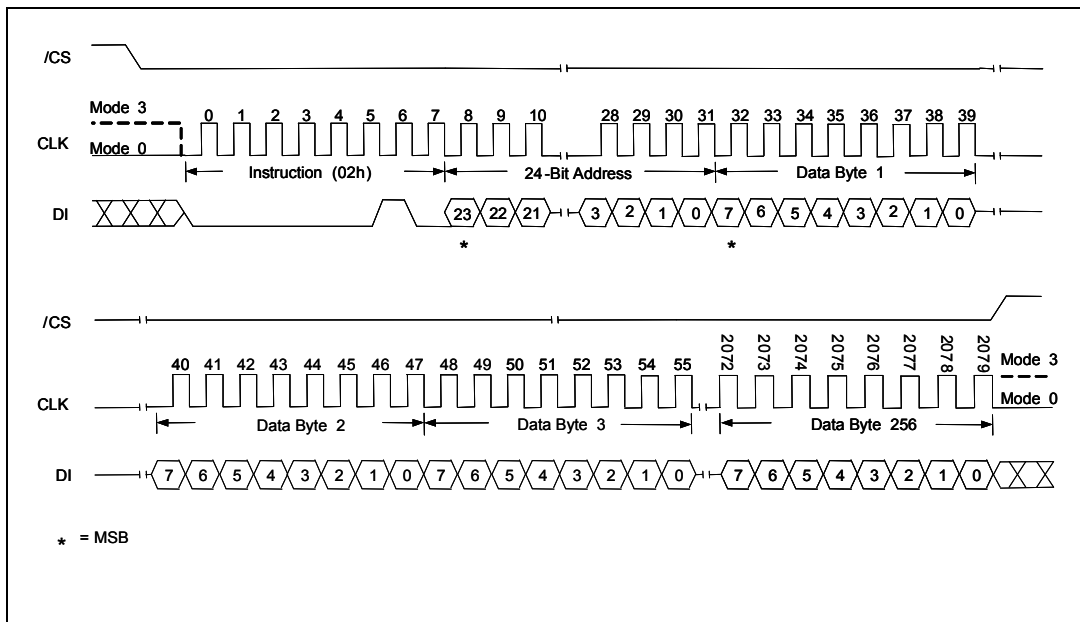

Figure 13. Page Program Instruction Sequence Diagram

11.2.14 Quad Data Input Page Program (32h)

The Quad Data Input Page Program instruction allows up to 256 bytes of data to be programmed at previously erased (FFh) memory locations using four pins: IO_0, IO_1, IO_2 and IO_3. The Quad Data Input Page Program can improve performance for PROM Programmer and applications that have slow clock speed <5MHz. System with faster clock speed will not realize much benefit for the Quad Data Input Program instruction since the inherent page program time is much greater than the time it takes to clock-in the data.

To use Quad Data Input Page Program the Quad Enable in Status Register-2 must be set (QE=1), A Write Enable instruction must be executed before the device will accept the Quad Data Input Page Program instruction (Status Register-1, WEL=1). The instruction is initiated by driving the /CS pin low and then shifting the instruction code "32h" followed by a 24-bit address (A23-A0) and at least one data, into the IO pins. The /CS pin must be held low for the entire length of the instruction while data is being sent to the device. All other functions of Quad Data Input Page Program are identical standard Page Program. The Quad Data Input Page Program instruction sequence is shown in figure 14.

Figure 14. Quad Data Input Page Program Instruction Sequence Diagram

11.2.15 Quad Page Program (38h)

The Quad Page Program instruction allows 24-bit address and up to 256 bytes of data to be programmed at previously erased (FFh) memory locations using four pins: IO_0, IO_1, IO_2 and IO_3. The Quad Page Program can improve performance for PROM Programmer and applications that have slow clock speed <5MHz. System with faster clock speed will not realize much benefit for the Quad Page Program instruction since the inherent page program time is much greater than the time it takes to clock-in the data.

To use Quad Page Program the Quad Enable in Status Register-2 must be set (QE=1), A Write Enable instruction must be executed before the device will accept the Quad Page Program instruction (Status Register-1, WEL=1). The instruction is initiated by driving the /CS pin low then shifting the instruction code "38h" followed by a 24-bit address (A23-A0) and at least one data, into the IO pins. The /CS pin must be held low for the entire length of the instruction while data is being sent to the device. All other functions of Quad Page Program are identical standard Page Program. The Quad Page Program instruction sequence is shown in figure 15.

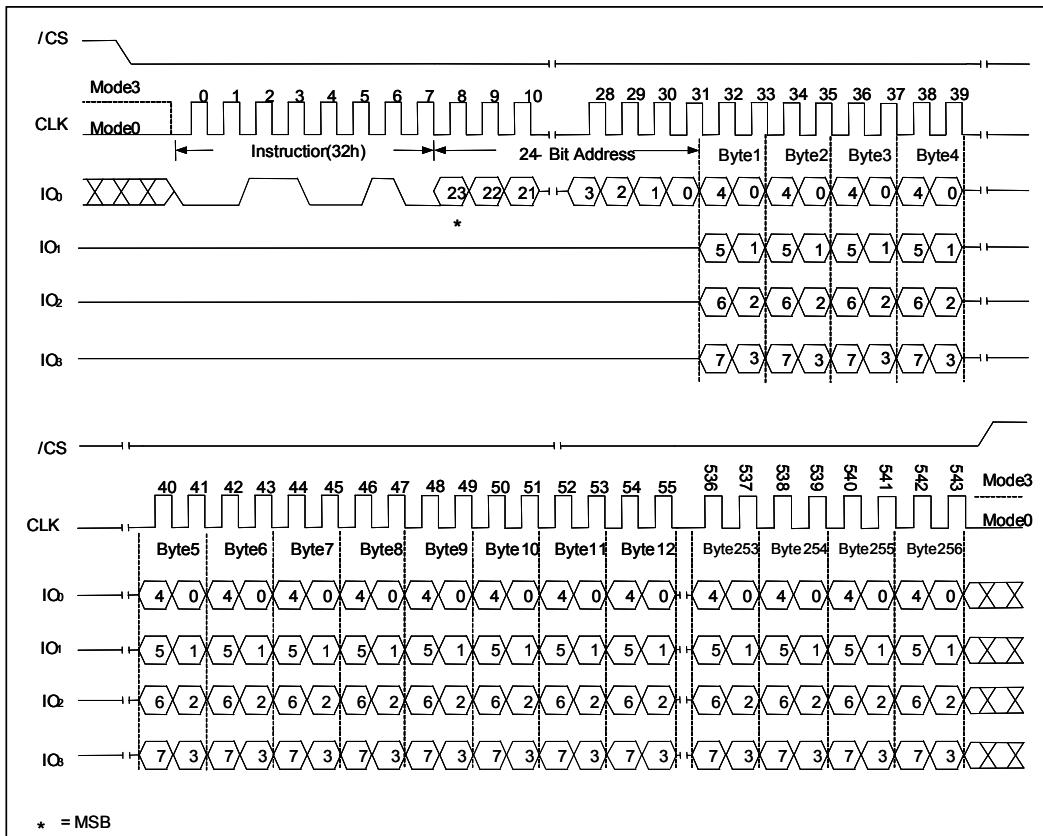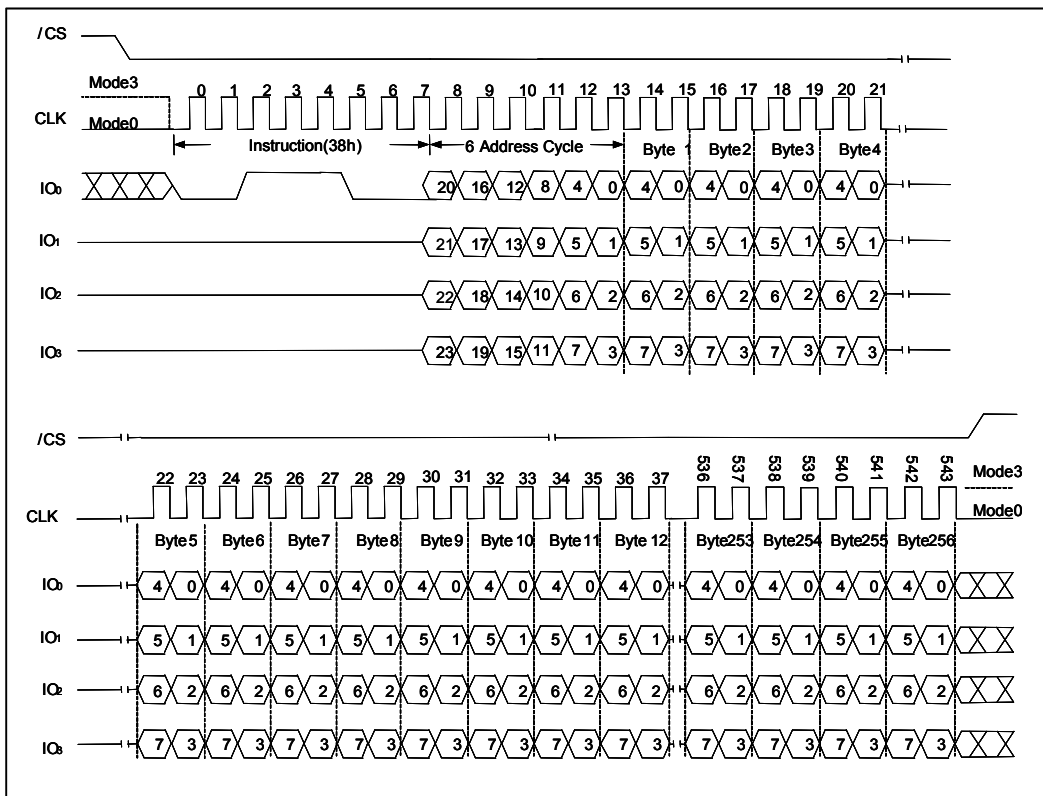Figure 15. Quad Page Program Instruction Sequence Diagram

11.2.16 Sector Erase (20h)

The sector Erase instruction sets all memory within a specified sector (4K-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Sector Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code "20h" followed a 24-bit sector address (A23-A0). The Sector Erase instruction sequence is shown in figure 16.

The /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Sector Erase instruction will not be executed. After /CS is driven high, the self-timed Sector Erase instruction will commence for a time duration of tSE (See AC Characteristics). While the Sector Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Sector Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Sector Erase cycle has finished the Write Enable Latch (WEL) bit in Status Register is cleared to 0. The Sector Erase instruction will not be executed if the addressed page is protected by the Block Protect (SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory protection table).

Figure 16. Sector Erase Instruction Sequence Diagram

11.2.17 32KB Block Erase (52h)

The Block Erase instruction sets all memory within a specified block (32k-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code "52h" followed a 24-bit block address (A23-A0). The Block Erase instruction sequence is shown in figure 17.

The /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After /CS is driven high, the self-timed Block Erase instruction will commence for a time duration of tBE1 (See AC Characteristics). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Block Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again.

After the Sector Erase cycle has finished the Write Enable Latch (WEL) bit in Status Register is cleared to 0.The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory Protection table).
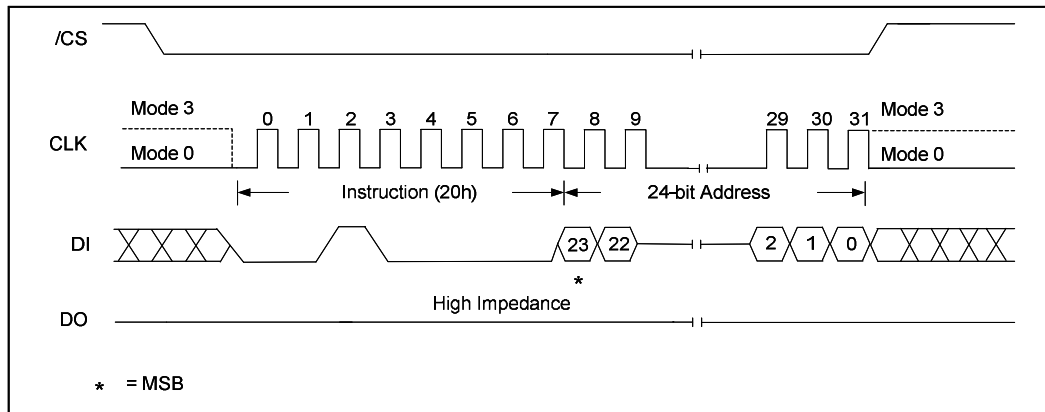

Figure 17. 32KB Block Erase Instruction Sequence Diagram

11.2.18 64KB Block Erase (D8h)

The Block Erase instruction sets all memory within a specified block (64k-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code "D8h" followed a 24-bit block address (A23-A0). The Block Erase instruction sequence is shown in figure 18.

The /CS pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After /CS is driven high, the self-timed Block Erase instruction will commence for a time duration of tBE1 (See AC Characteristics). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the BUSY bit. The BUSY bit is a 1 during the Block Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Block Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory Protection table).
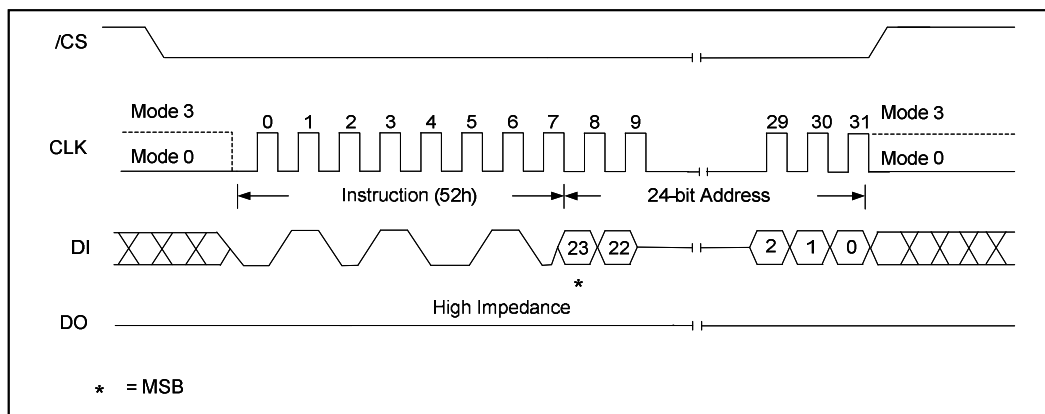

Figure 18. 64KB Block Erase Instruction Sequence Diagram

11.2.19 Chip Erase (C7h / 60h)

The Chip Erase instruction sets all memory within the device to the erased sate of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Chip Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the /CS pin low and shifting the instruction code "C7h" or "60h". The Chip Erase instruction sequence is shown in figure 19.

The /CS pin must be driven high after the eighth bit has been latched. If this is not done the Chip Erase instruction will not be executed. After /CS is driven high, the self-timed Chip Erase instruction will commence for a time duration of tCE (See AC Characteristics). While the Chip Erase cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the BUSY bit. The BUSY bit is a 1 during the Chip Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Chip Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Chip Erase instruction will not be executed if any page is protected by the Block Protect (SEC, TB, BP2, BP1, and BP0) bits (see Status Register Memory Protection table).

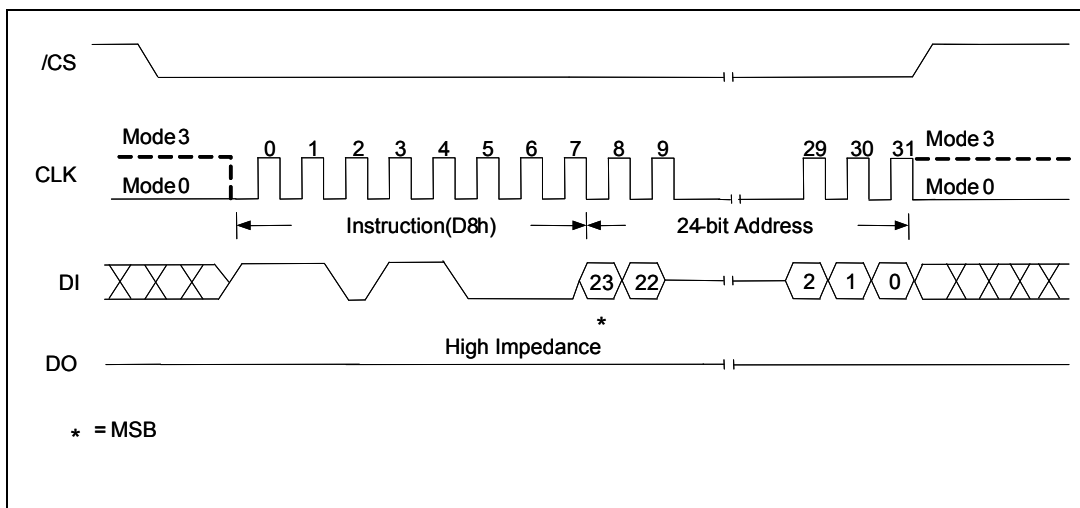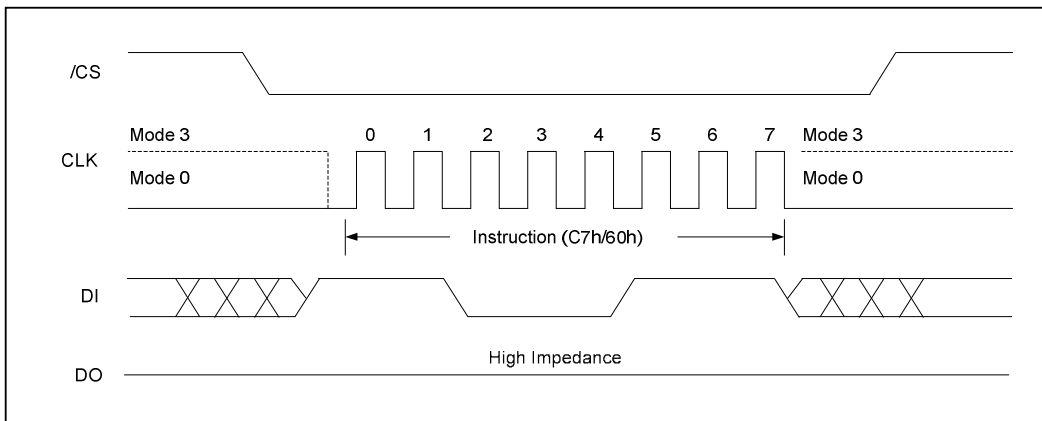Figure 19. Chip Erase Instruction Sequence Diagram

11.2.20 Erase / Program Suspend (75h)

The Erase/Program Suspend instruction "75h", allows the system to interrupt a Sector or Block Erase operation or a Page Program operation and then read from or program/erase data to, any other sectors or blocks. The Erase/Program Suspend instruction sequence is shown in figure 20.

The Write Status Register instruction (01h) and Erase instructions (20h, 52h, D8h, C7h, 60h, 44h) are not allowed during Erase Suspend. Erase Suspend is valid only during the Sector or Block erase operation. If written during the Chip Erase operation, the Erase Suspend instruction is ignored. The Write Status Register instruction (01h) and Program instructions (02h, 32h, 42h) are not allowed during Program Suspend. Program Suspend is valid only during the Page Program or Quad Page Program operation.

The Erase/Program Suspend instruction "75h" will be accepted by the device only if the SUS bit in the Status Register equals to 0 and the BUSY bit equals to 1 while a Sector or Block Erase or a Page Program operation is on-going. If the SUS bit equals to 1 or the BUSY bit equals to 0, the Suspend instruction will be ignored by the device. A maximum of time of "tSUS" (See AC Characteristics) is required to suspend the erase or program operation. The BUSY bit in the Status Register will be cleared from 1 to 0 within "tSUS" and the SUS bit in the Status Register will be set from 0 to 1 immediately after Erase/Program Suspend. For a previously resumed Erase/Program operation, it is also required that the Suspend instruction "75h" is not issued earlier than a minimum of time of "tSUS" following the preceding Resume instruction "7Ah".

Unexpected power off during the Erase/Program suspend state will reset the device and release the suspend state. SUS bit in the Status Register will also reset to 0. The data within the page, sector or block that was being suspended may become corrupted. It is recommended for the user to implement system design techniques against the accidental power interruption and preserve data integrity during erase/program suspend state.
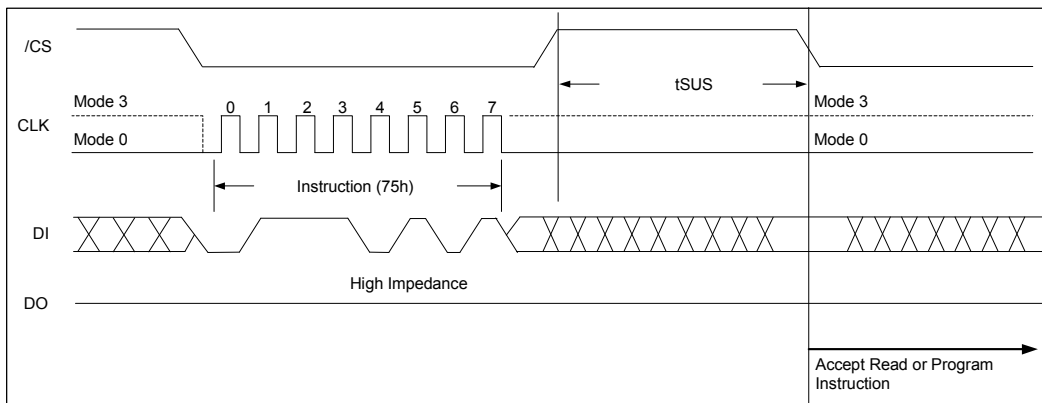
Figure 20. Erase Suspend instruction Sequence

11.2.20 Erase / Program Resume (7Ah)

The Erase/Program Resume instruction "7Ah" must be written to resume the Sector or Block Erase operation or the Page Program operation after an Erase/Program Suspend. The Resume instruction "7Ah" will be accepted by the device only if the SUS bit in the Status Register equals to 1 and the BUSY bit equals to 0. After issued the SUS bit will be cleared from 1 to 0 immediately, the BUSY bit will be set from 0 to 1 within 200ns and the Sector or Block will complete the erase operation or the page will complete the program operation. If the SUS bit equals to 0 or the BUSY bit equals to 1, the Resume instruction "7Ah" will be ignored by the device. The Erase/Program Resume instruction sequence is shown in figure 20.

Resume instruction is ignored if the previous Erase/Program Suspend operation was interrupted by unexpected power off. It is also required that a subsequent Erase/Program Suspend instruction not to be issued within a minimum of time of "t SUS" following a previous Resume instruction.

Figure 20. Erase / Program Resume instruction Sequence

11.2.22 Power-down (B9h)

Although the standby current during normal operation is relatively low, standby current can be further reduced with the Power-down instruction. The lower power consumption makes the Power-down instruction especially useful for battery powered applications (See ICC1 and ICC2 in AC Characteristics). The instruction is initiated by driving the /CS pin low and shifting the instruction code "B9h" as shown in figure 22.

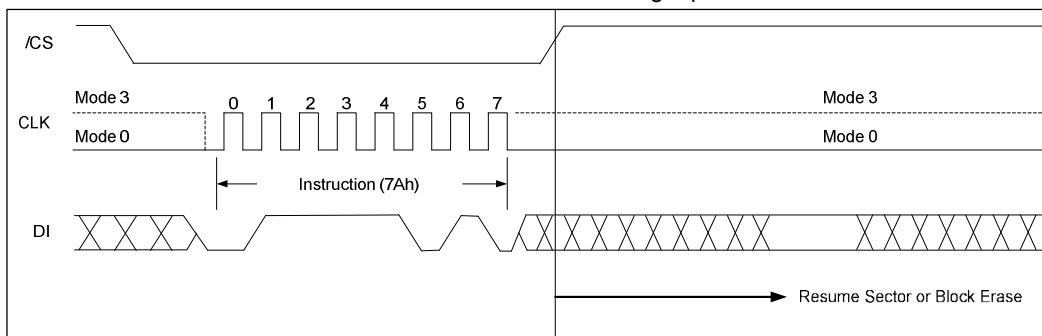The /CS pin must be driven high after the eighth bit has been latched, If this is not done the Power-down instruction will not be executed. After /CS is driven high, the Power-down state will be entered within the time duration of tDP (See AC Characteristics). While in the Release power-down /Device ID instruction, which restores the device to normal operation, will be recognized. All other instructions are ignored. This includes the Read Status Register instruction, which is always available during normal operation. Ignoring all but one instruction makes the Power Down state a useful condition for securing maximum write protection. The device always powers-up in the normal operation with the standby current of ICC1.
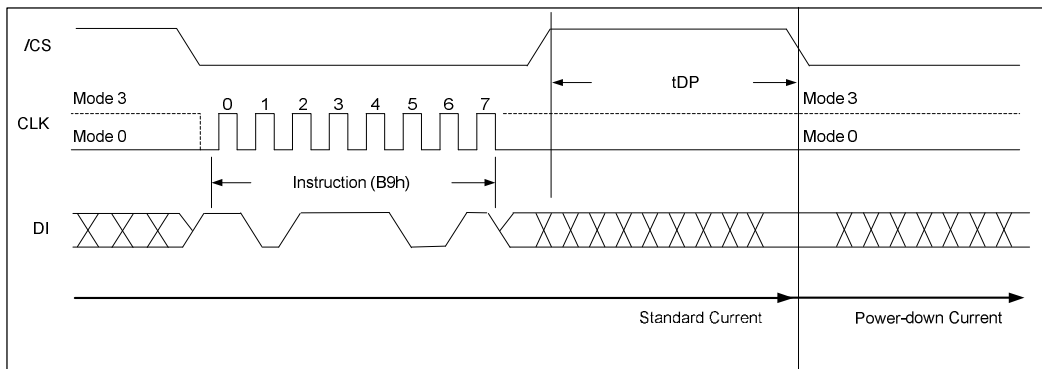
Figure 22. Deep Pwer-down Instruction Sequence Diagram

11.2.23 Release Power-down / Device ID (ABh)

The Release from Power-down / Device ID instruction is a multi-purpose instruction. It can be used to release the device from the power-down state or obtain the device electronic identification (ID) number.

To release the device from the power-down state, the instruction is issued by driving the /CS pin low, shifting the instruction code "ABh" and driving /CS high as shown in figure 23a. Release from power-down will take the time duration of tRES1 (See AC Characteristics) before the device will resume normal operation and other instructions are accepted. The /CS pin must remain high during the tRES1 time duration.

When used only to obtain the Device ID while not in the power-down state, instruction is initiated by driving the /CS pin low and shifting the instruction code "ABh" followed by 3-dummy bytes. The Device ID bits are then shifted on the falling edge of CLK with most significant bit (MSB) first as shown in figure 23b. The Device ID value for the FM25Q32 is listed in Manufacturer and Device Identification table. The Device ID can be read continuously. The instruction is completed by driving /CS high.

When used to release the device from the power-down state and obtain the Device ID, the

instruction is the same as previously described, and shown in figure 23b, except that after /CS is driven high it must remain high for a time duration of tRES2 (See AC Characteristics). After this time duration the device will resume normal operation and other instructions will be accepted. If the Release from power-down /Device ID instruction is issued while an Erase, Program or Write cycle is in process (when BUSY equals 1) the instruction is ignored and will not have any effects on the current cycle.
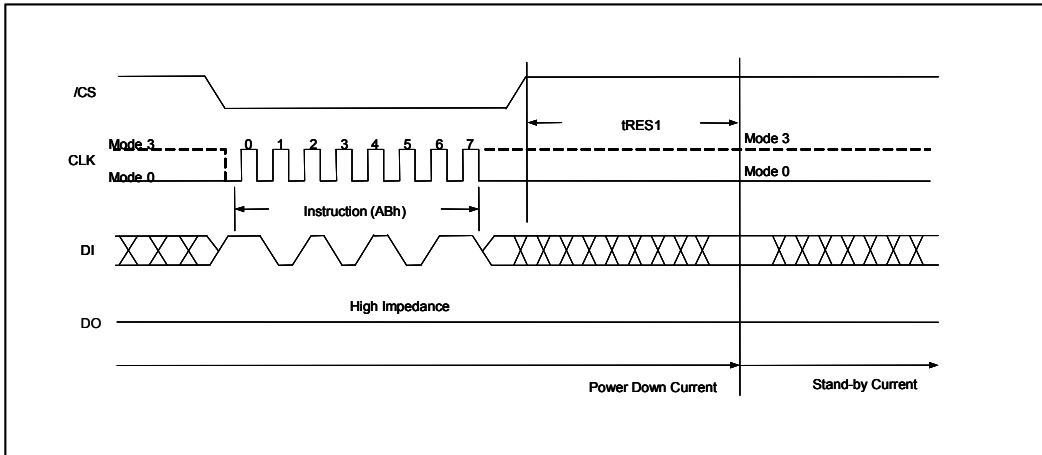
Figure 23a. Release power-down Instruction Sequence
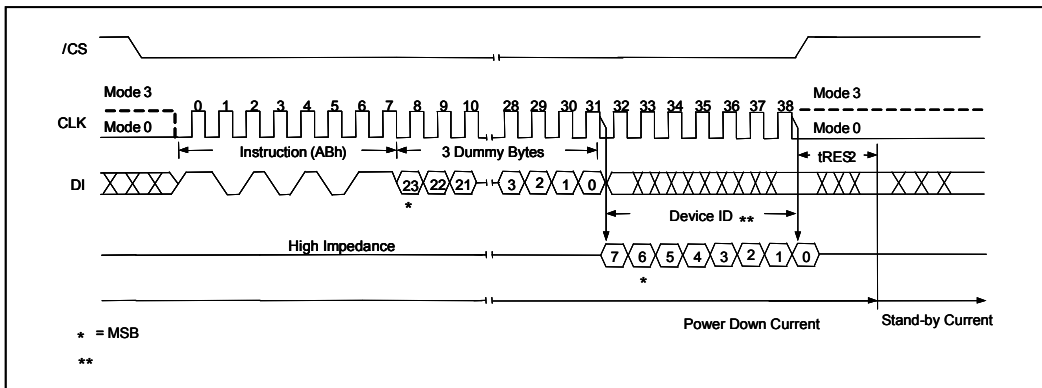
Figure 23b. Release power-down / Device ID Instruction Sequence Diagram

11.2.24 Read Manufacturer/ Device ID (90h),(EFh),(DFh)

The Read Manufacturer/ Device ID instruction is an alternative to the Release from Power-down / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID.

The Read Manufacturer/ Device ID instruction is very similar to the Release from Power-down / Device ID instruction. The instruction is initiated by driving the /CS pin low and shifting the instruction code "90h" or "EFh" or "DFh" followed by a 24-bit address (A23-A0) of 000000h. After which, the Manufacturer ID for FIDELIX SEMICONDUCTOR (F8h) and the Device ID are shifted out on the falling edge of CLK with most significant bit(MSB) first as shown in figure 24a, 24b or 24c. The Device ID value for the FM25Q32 is listed in Manufacturer and Device Identification table. If the 24-bit address is initially set to 000001h the Device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving/CS high.
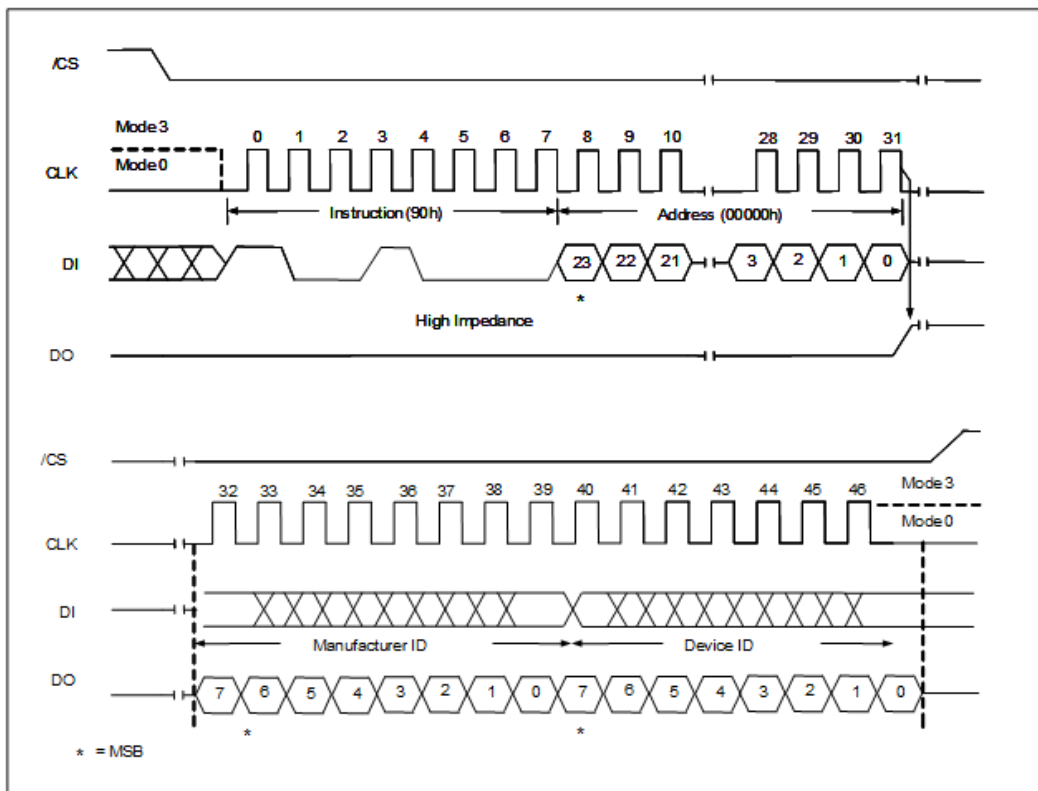
Figure 24a. Read Manufacturer/ Device ID Diagram
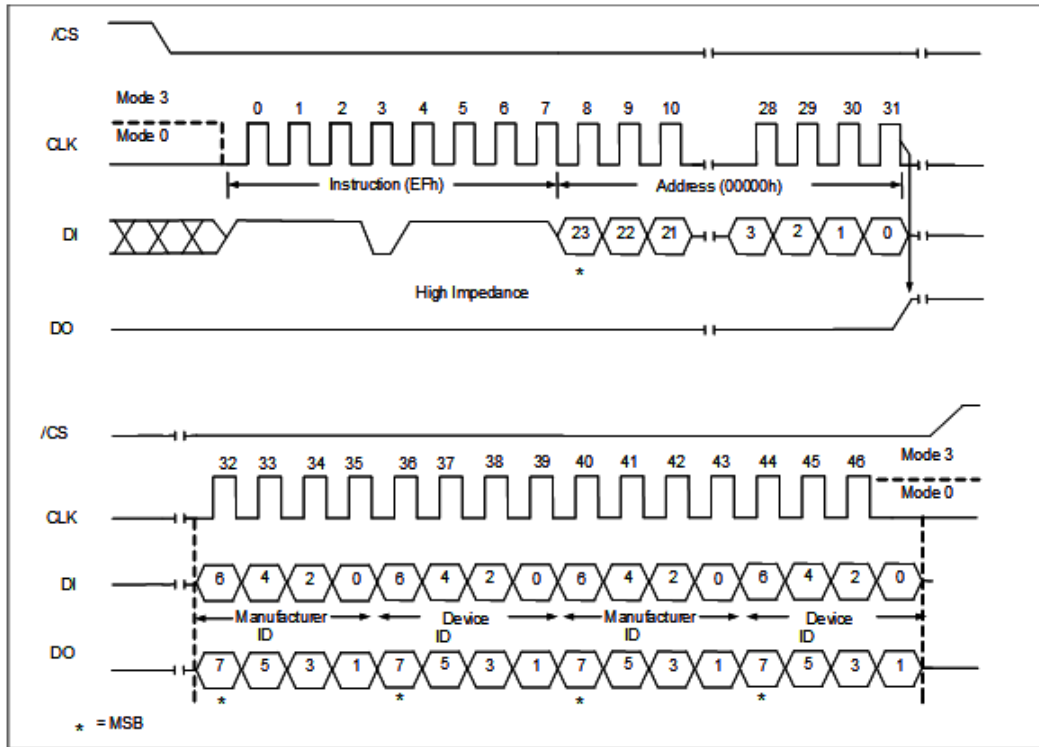
Figure 23b. Read Dual Manufacturer/ Device ID Diagram
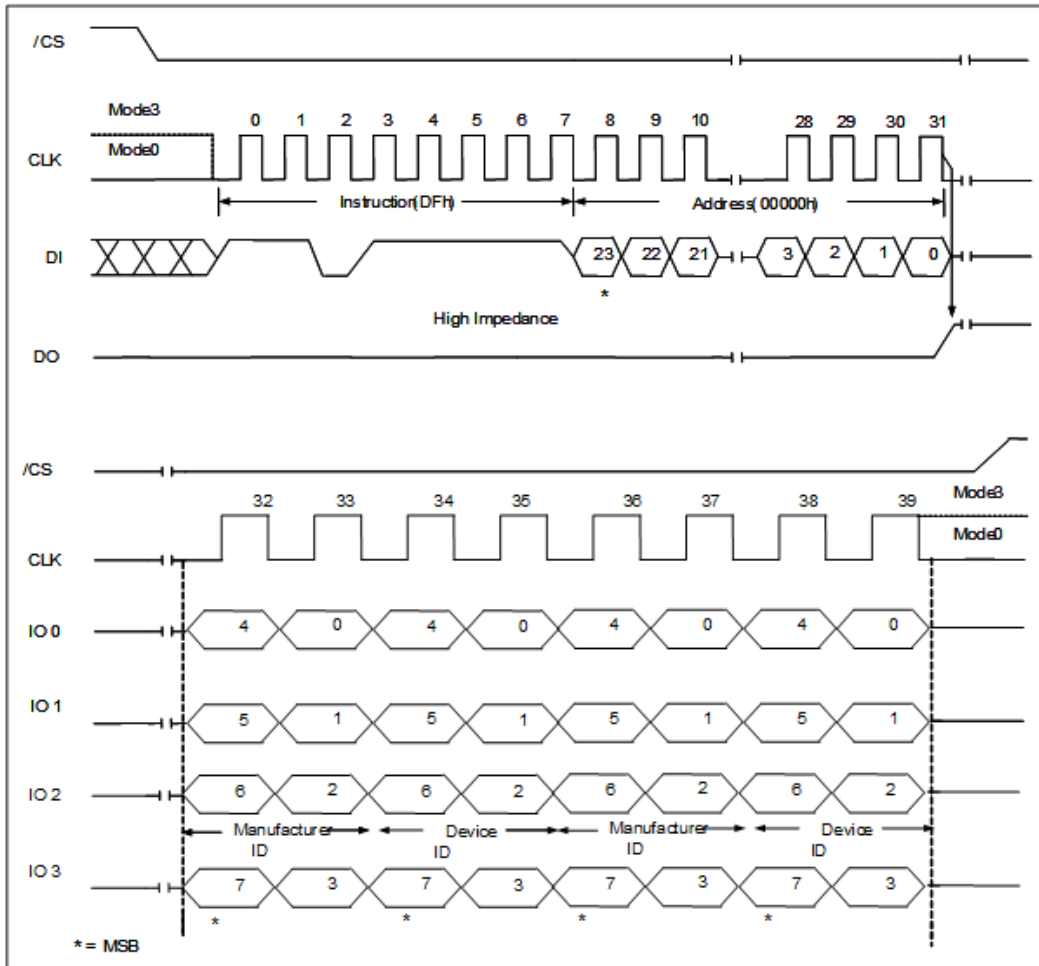
Figure 23c. Read Quad Manufacturer/ Device ID Diagram

11.2.25 JEDEC ID (9Fh)

For compatibility reasons, the FM25Q32 provides several instructions to electronically determine the identity of the device. The Read JEDEC ID instruction is compatible with the JEDEC standard for SPI compatible serial memories that was adopted in 2003. The instruction is initiated by driving the /CS pin low and shifting the instruction code "9Fh". The instruction JEDEC assigned Manufacturer ID byte for FIDELIX SEMICONDUCTOR(F8h) and two Device ID bytes, Memory Type(ID-15-ID8) and Capacity (ID7-ID0) are then shifted out on the falling edge of CLK with most significant bit (MSB) first shown in figure 25. For memory type and capacity values refer to Manufacturer and Device Identification table. The JEDEC ID can be read continuously. The instruction is completed by driving/CS high.
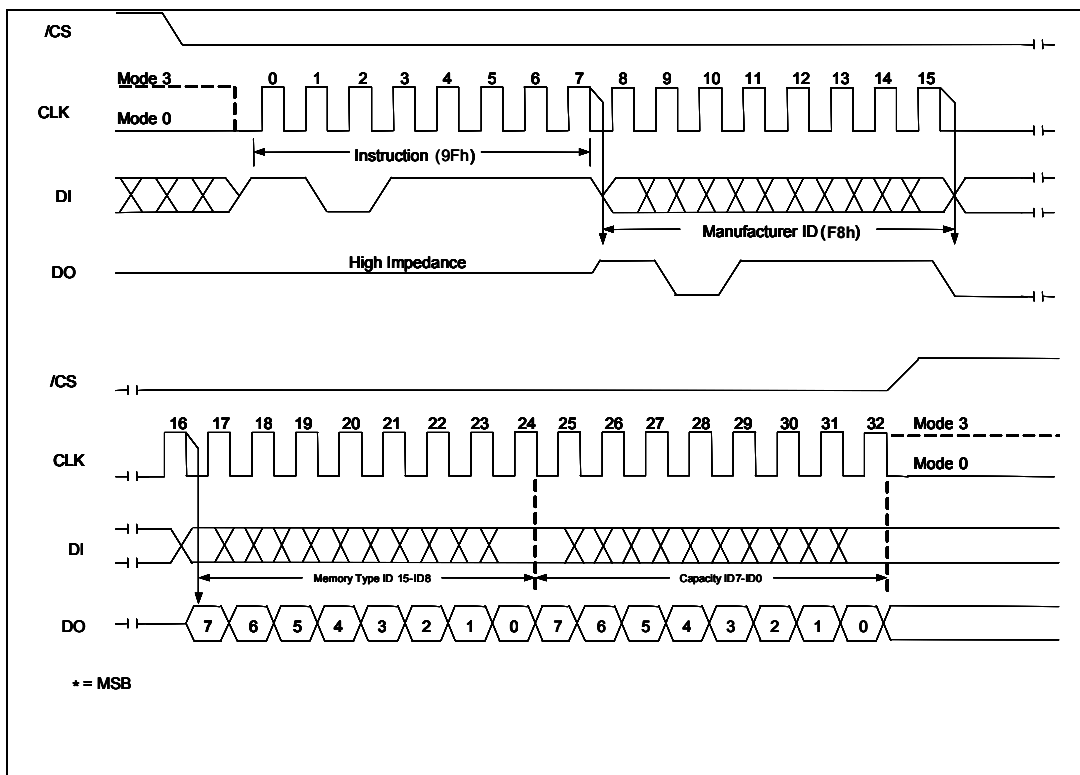
Figure 25. Read JEDEC ID

11.2.26 Mode Bit Reset (FFh)

For Fast Read Dual/Quad I/O operations, Mode Bits (M7-0) are implemented to further reduce instruction overhead. By setting the Mode Bits (M7-0) to "Ax" hex, the next Fast Read Dual/Quad I/O operations do not require the BBh/EBh instruction code (See 11.2.10 Fast Read Dual I/O and 11.2.11   Fast Read Quad I/O for detail descriptions).

If the system controller is reset during operation it will likely send a standard SPI instruction, such as Read ID (9Fh) or Fast Read (0Bh), to the FM25Q32. However, as with most SPI Serial Flash memories, the FM25Q32 does not have a hardware Reset pin, so if Mode bits are set to "Ax" hex, the FM25Q32 will not recognize any standard SPI instruction. To address this possibility, it is recommended to issue a Mode Bit Reset instruction "FFh" as the first instruction after a system Reset. Doing so will release the mode Bits for the "Ax" hex state and allow Standard SPI instruction to be recognized. The Mode Bits Reset instruction is shown in figure 26.
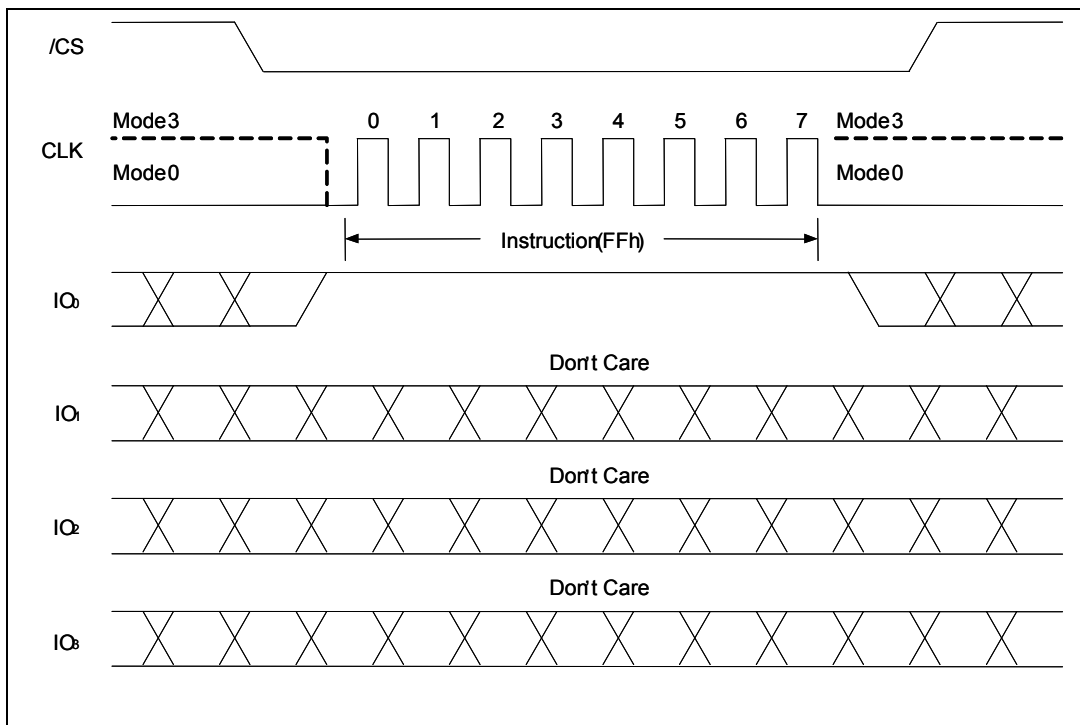
Figure 26. Mode Bits Reset for Fast Read Dual/Quad I/O

11.2.27 Enter Secured OTP (B1h)

The Enter Secured OTP instruction is for entering the additional 4K-bit secured OTP mode. The additional 4K-bit secured OTP is independent from main array, which may be used to store unique serial number for system identifier. After entering the Secured OTP mode, and then follow standard read or program, procedure to read out the data or update data. The Secured OTP data cannot be updated again once it is lock-down

Please note that WRSR/WRSCUR commands are not acceptable during the access of secure OTP region, once security OTP is lock down, only commands related with read are valid.
The Enter Secured OTP instruction sequence is shown in figure 27.
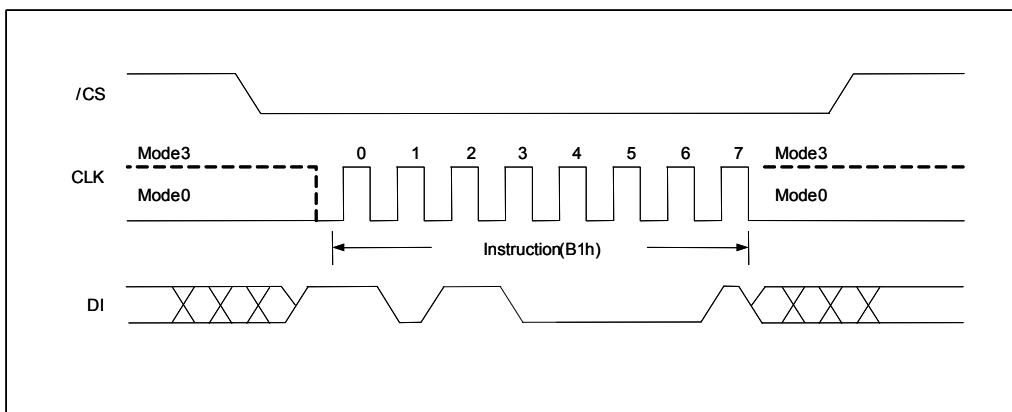
Figure 27. Enter Secured OTP instruction sequence

11.2.28 Exit Secured OTP (C1h)

The Exit Secured OTP instruction is for exiting the additional 4K-bit secured OTP mode.
The Exit Secured OTP instruction sequence is shown in figure 28
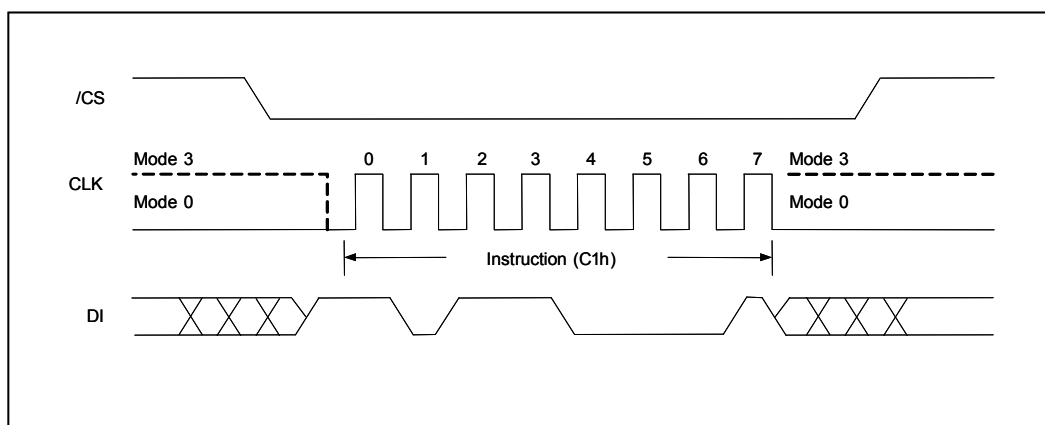
Figure 28. Exit Secured OTP instruction sequence

11.2.29 Read Security Register (2Bh)

The Read Security Register instruction is for reading the value of Security Register bits. The Read Security Register can be read at any time (even in program/erase/write status register condition) and continuously.

The definition of the Security Register bits is as below:

Secured OTP Indicator bit. The Secured OTP indicator bit shows the chip is locked by factory before ex-factory or not. When it is "0", it indicates non-factory lock, "1" indicates factory-lock.

Lock-down Secured OTP (LDSO) bit. By writing WRSCUR instruction, the LDSO bit may be set to "1" for customer lock-down purpose. However, once the bit it set to "1" (Lock-down), the LDSO bit and the 4K-bit Secured OTP area cannot be updated any more. While it is in 4K-bit Secured OTP mode, array access is not allowed to write.
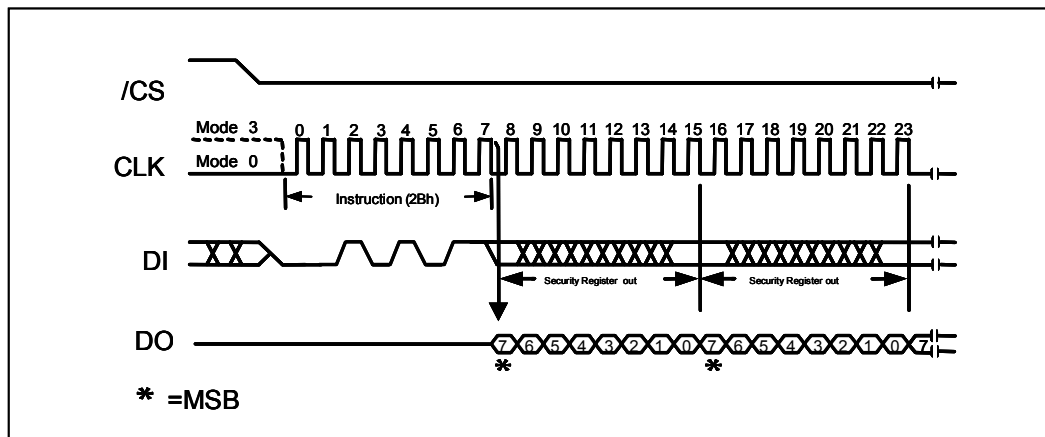
Figure 29. Read Security Register instruction sequence

Security Register Definition

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
x	x	x	x	x	x	LDSO (indicate if lock-down)	Secured OTP indicator bit
reserved	reserved	reserved	reserved	reserved	reserved	0 = not lock-down 1 = lock-down(cannot program/erase OTP)	0 = non factory lock 1 = factory lock
Volatile bit	Volatile bit	Volatile bit	Volatile bit	Volatile bit	Volatile bit	Non-Volatile bit	Non-Volatile bit

11.2.30 Write Security Register (2Fh)

The Write Security Register instruction is for changing the values of Security Register bits. Unlike Write Status Register, the WREN instruction is not required before writing WRSCUR instruction. The WRSCUR instruction may change the value of bit1 (LDSO bit) for customer to lock-down the 4K-bit Secured OTP area. Once the LDSO bit is set to "1", the Secured OTP area cannot be updated any more.

The /CS must go high exactly at the boundary; otherwise, the instruction will be rejected and not executed.
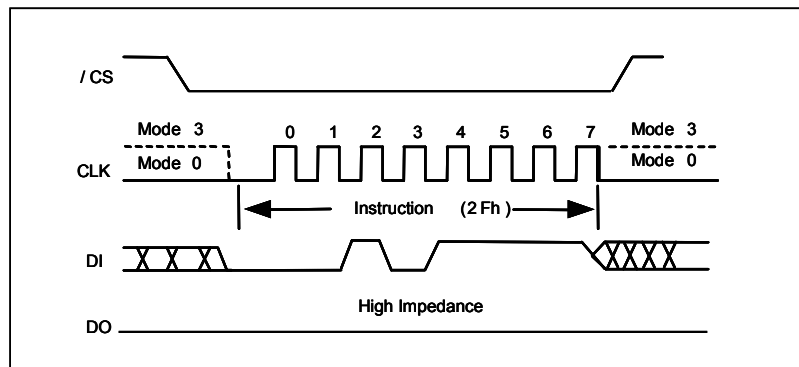
Figure 30. Write Security Register instruction sequence

11.2.31 4K-bit Secured OTP

It's for unique identifier to provide 4K-bit one-time-program area for setting device unique serial number which may be set by factory or system customer. Please refer to table of "4K-bit secured OTP definition".

 - Security register bit 0 indicates whether the chip is locked by factory or not.
 - To program the 4K-bit secured OTP by entering 4K-bit secured OTP mode (with ENSO command) and going through normal program procedure, and then exiting 4K-bit secured OTP mode by writing EXSO command
 - Customer may lock-down bit1 as "1". Please refer to "table of security register definition" for security register bit definition and table of "4K-bit secured OTP definition" for address range definition.
 - Note. Once lock-down whatever by factory or customer, it cannot be changed any more. While in 4K-bit secured OTP mode, array access is not allowed to write.

4K-bit secured OTP definition

Address range	Size	Standard Factory Lock	Customer Lock
000000 ~ 00000F	128-bit	ESN (Electrical Serial Number)	Determined by customer
000010 ~ 0001FF	3968-bit	N/A	

11.2.32 Set Burst with Wrap (77h)

The Set Burst with Wrap (77h) instruction is used in conjunction with "Fast Read Quad I/O" and "Word Read Quad I/O" instructions to access a fixed length of 8/16/32/64-byte section within a 256-byte page. Certain applications can benefit from this feature and improve the overall system code execution performance.

Similar to a Quad I/O instruction, the Set Burst with Wrap instruction is initiated by driving the /CS pin low and then shifting the instruction code "77h" followed by 24 dummy bits and 8 "Wrap Bits", W7-0. The instruction sequence is shown in Set Burst with Wrap Instruction Sequence.

Wrap bit W7 and the lower nibble W3-0 are not used.

W6, W5		W4 = 0		W4 = 1(Default)	
		Wrap Around	Wrap Length	Wrap Around	Wrap Length
0	0	Yes	8-byte	No	N/A
0	1	Yes	16-byte	No	N/A
1	0	Yes	32-byte	No	N/A
1	1	Yes	64-byte	No	N/A

Once W6-4 is set by a Set Burst with Wrap instruction, all the following "Fast Read Quad I/O" and instructions will use the W6-4 setting to access the 8/16/32/64-byte section within any page. To exit the "Wrap Around" function and return to normal read operation, another Set Burst with Wrap instruction should be issued to set W4 = 1. The default value of W4 upon power on is 1. In the case of a system Reset while W4 = 0, it is recommended that the controller issues a Set Burst with Wrap instruction to reset W4 = 1 prior to any normal Read instructions since FM25Q32 does not have a hardware Reset Pin.
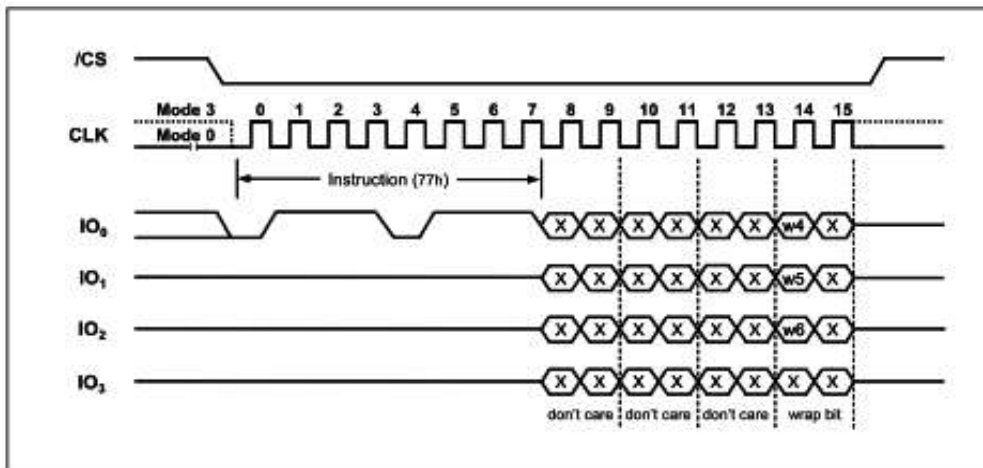
Set Burst with Wrap Instruction Sequence

12. ELECTRICAL CHARACTERISTICS

12.1 Absolute Maximum Ratings [1]

PARAMETERS	SYMBOL	CONDITIONS	RANGE	UNIT
Supply Voltage	VCC		-0.6 to +4.0	V
Voltage Applied to Any Pin	VIO	Relative to Ground	-0.6 to VCC +0.4	V
Transient Voltage on any Pin	VIOT	<20nS Transient Relative to Ground	-2.0V to VCC +2.0V	V
Storage Temperature	TSTG		-65 to +150	˚C
Lead Temperature	TLEAD		See Note[3]	˚C
Electrostatic Discharge Voltage	VESD	Human Body Model[4]	-2000 to +2000	V

Notes:
1. Specification for FM25Q32 is preliminary. See preliminary designation at the end of this document.
2. This device has been designed and tested for the specified operation ranges. Proper operation outside of these levels is not guaranteed. Exposure to absolute maximum ratings may affect device reliability. Exposure beyond absolute maximum ratings may cause permanent damage.
3. Compliant with JEDEC Standard J-STD-20C for small body Sn-Pb or Pb-free (Green) assembly and the European directive on restrictions on hazardous substances (RoHS) 2002/95/EU.
4. JEDEC Std JESD22-A114A (C1=100pF, R1=1500 ohms, R2=500 ohms).

12.2 Operating Ranges

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
Erase/Program Cycles	VCC	FR1 = 85MHz (Single/Dual/Quad SPI)	2.7	3.6	V
		FR2 = 104MHz (Single/Dual/Quad SPI)	3.0		
		fR = 50MHz (Read Data 03h)	2.7		
Temperature,Operating	Tj	Industrial	-40	+85	˚C

12.3 Endurance and Data Retention

PARAMETER	CONDITIONS	MIN	MAX	UNIT
Erase/Program Cycles	4KB sector, 32/64KB block or full chip.	100,000		Cycles
Data Retention	Full Temperature Range		20	years

12.4 Power-up Timing and Write Inhibit Threshold

PARAMETER	SYMBOL	SPEC		UNIT
		MIN	MAX	
VCC(min) to /CS Low	tVSL[1]	10		μs
Time Delay Before Write Instruction	tPUW[1]	1	10	ms
Write Inhibit Threshold Voltage	VWI[1]	1	2	V

Note:

1. These parameters are characterized only.
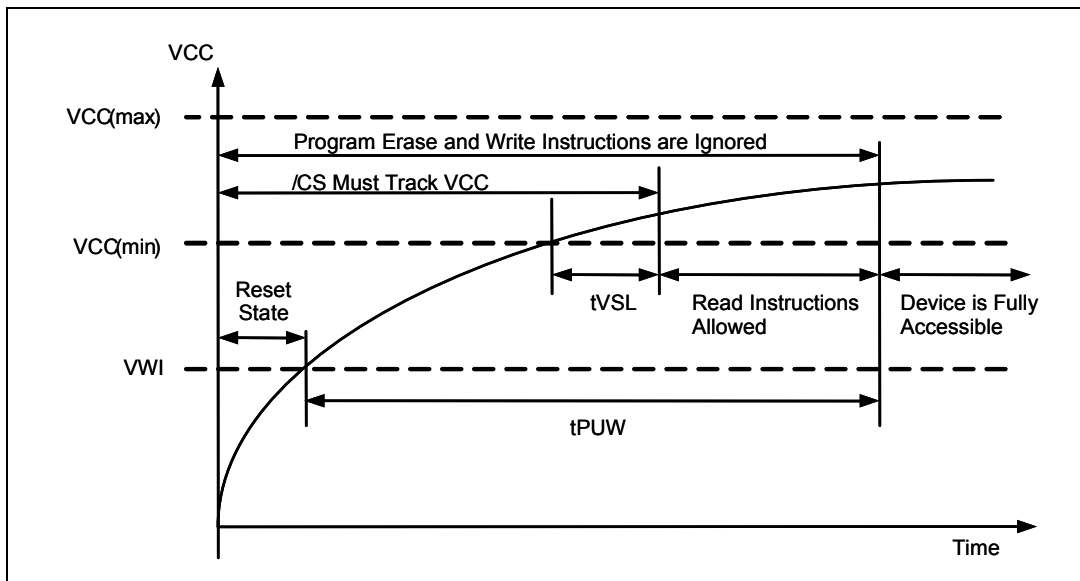
Figure 30. Power-up Timing and Voltage Levels

12.5 DC Electrical Characteristics

PARAMETER	SYMBOL	CONDITION	SPEC			UNIT
			MIN	TYP	MAX	
Input Capacitance	CIN[1]	VIN=0V[2]			6	pF
Output Capacitance	COUT[1]	VOUT=0V[2]			8	pF
Input Leakage	ILI				±2	μA
I/O Leakage	ILO				±2	μA
Standby Current	ICC1	/CS=VCC, VIN=GND or VCC		10	50	μA
Power-down Current	ICC2	/CS=VCC, VIN=GND or VCC		1	5	μA
Current Read Data/ Dual/Quad 1㎒[2]	ICC3	C=0.1 VCC / 0.9VCC IO=Open		4/5/6	6/7.5/9	mA
Current Read Data/ Dual/Quad 33㎒[2]	ICC3	C=0.1 VCC / 0.9VCC IO=Open		6/7/8	9/10.5/12	mA
Current Read Data/ Dual/Quad 50㎒[2]	ICC3	C=0.1 VCC / 0.9VCC IO=Open		7/8/9	10/12/13.5	mA
Current Read Data/ Dual/Quad 85㎒[2]	ICC3	C=0.1 VCC / 0.9VCC IO=Open		10/11/12	15/16.5/18	mA
Current Write Status Register	ICC4	/CS=VCC		8	12	mA
Current page Program	ICC5	/CS=VCC		20	25	mA
Current Sector/Block Erase	ICC6	/CS=VCC		20	25	mA
Current Chip Erase	ICC7	/CS=VCC		20	25	mA
Input Low Voltages	VIL		-0.5		VCC x0.2	V
Input High Voltages	VIH		VCC x0.8		VCC +0.4	V
Output Low Voltages	VOL	IOL=1.6㎃			0.4	V
Output High Voltages	VOH	IOH=-100μA	VCC -0.2			V

Notes:

1. Tested on sample basis and specified through design and characterization data, TA = 25˚C, VCC = 3V.
2. Checked Board Pattern.

12.6 AC Measurement Conditions

PARAMETER	SYMBOL	SPEC		UNIT
		MIN	MAX	
Load Capacitance	C_L		30	pF
Input Rise and Fall Times	T_R, T_F		5	ns
Input Pulse Voltages	V_{IN}	0.2 VCC to O. 8 VCC		V
Input Timing Reference Voltages	IN	0.3 VCC to O. 7 VCC		V
Output Timing Reference Voltages	OUT	0.5 VCC to O. 5 VCC		V

Note:

1. Output Hi-Z is defined as the point where data out is no longer driven.
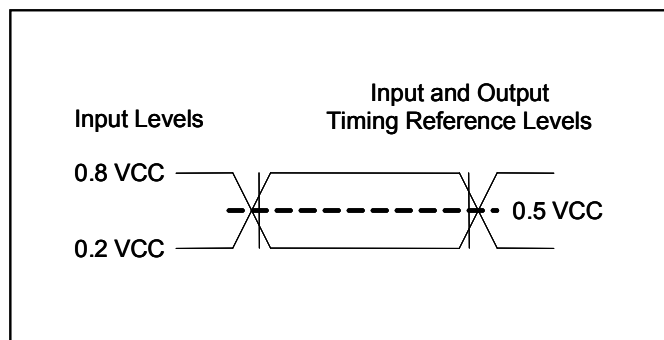
Figure 31. AC Measurement I/O Waveform

12.7 AC Electrical Characteristics

DESCRIPTION	SYMBOL	ALT	SPEC			UNIT
			MIN	TYP	MAX	
Clock frequency For all instructions, except Read Data (03h) 2.7V-3.6V VCC & Industrial Temperature	FR1	f_c	D.C.		85	MHz
Clock frequency For all instructions, except Read Data (03h) 3.0V-3.6V VCC & Commercial Temperature	FR2	f_c	D.C.		104	MHz
Clock freq. Read Data instruction (03h)	f_R		D.C.		50	MHz
Clock High, Low Time except Read Data (03h)	tCLH, tCLL[1]		4			ns
Clock High, Low Time for Read Data (03h) instructions	tCRLH, tCRLL[1]		6			ns
Clock Rise Time peak to peak	tCLCH[2]		0.1			V/ns
Clock Fall Time peak to peak	tCHCL[2]		0.1			V/ns
/CS Active Setup Time relative to CLK	tSLCH	tCSS	7			ns
/CS Not Active Hold Time relative to CLK	tCHSL		5			ns
Data In Setup Time	tDVCH	tDSU	4			ns
Data In Hold Time	tCHDX	tDH	4			ns
/CS Active Hold Time relative to CLK	tCHSH		7			ns
/CS Not Active Setup Time relative to CLK	tSHCH		7			ns
/CS Deselect Time (for Read instructions/ Write, Erase and Program instructions)	tSHSL	tCSH	10/40			ns
Output Disable Time	tSHQZ[2]	tDIS			7	ns
Clock Low to Output Valid 2.7V-3.6V / 3.0V-3.6V	tCLQV	tV			7/6	ns
Output Hold Time	tCLQX	tHO	0			ns
/Hold Active Setup Time relative to CLK	tHLCH		7			ns

12.8 AC Electrical Characteristics (cont'd)

DESCRIPTION	SYMBOL	ALT	SPEC			UNIT
			MIN	TYP	MAX	
/HOLD Active Hold Time relative to CLK	tCHHH		5			ns
/HOLD Not Active Setup Time relative to CLK	tHHCH		7			ns
/HOLD Not Active Hold Time relative to CLK	tCHHL		5			ns
/HOLD to Output Low-Z	tHHQX[2]	t_{LZ}			7	ns
/HOLD to Output High-Z	tHLQZ[2]	t_{HZ}			12	ns
Write Protect Setup Time Before /CS Low	tWHSL[3]		20			ns
Write Protect Setup Time After /CS High	tSHWL[3]		100			ns
/CS High to Power-down Mode	tDP[2]				3	μs
/CS High to Standby Mode without Electronic Signature Read	tRES1[2]				3	μs
/CS High to Standby Mode with Electronic Signature Read	tRES2[2]				1.8	μs
/CS High to next Instruction after Suspend	tSUS[2]				20	μs
Write Status Register Time	tw			10	15	ms
Byte Program Time	t_{BP}			10	150	μs
Page Program Time	t_{PP}			1.5	5	ms
Sector Erase Time(4KB)	t_{SE}			40	300	ms
Block Erase Time(32KB)	t_{BE1}			200	1000	ms
Block Erase Time(64KB)	t_{BE2}			300	1500	ms
Chip Erase Time	t_{CE}			10	50	s

Notes:

1. Clock high + Clock low must be less than or equal to 1/fc.
2. Value guaranteed by design and/or characterization, not 100% tested in production.
3. Only applicable as a constraint for a Write Status Register instruction when Sector Protect Bit is set to 1.
4. Commercial temperature only applies to Fast Read (F_{R1} & F_{R2}). Industrial temperature applies to all other parameters.

12.9 Serial Output Timing
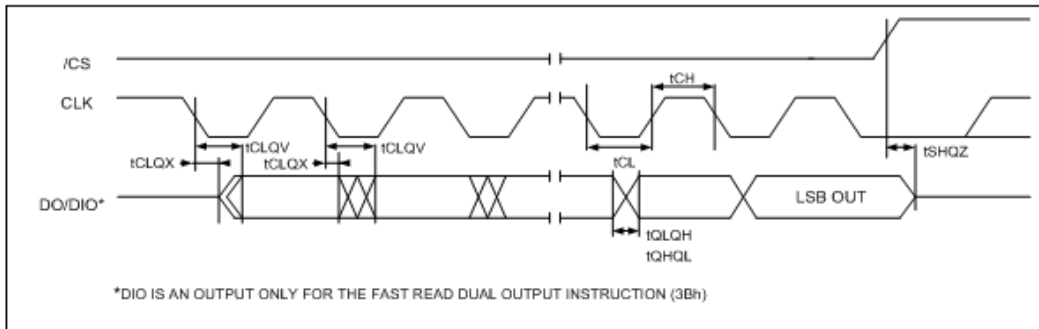
12.10 Input Timing
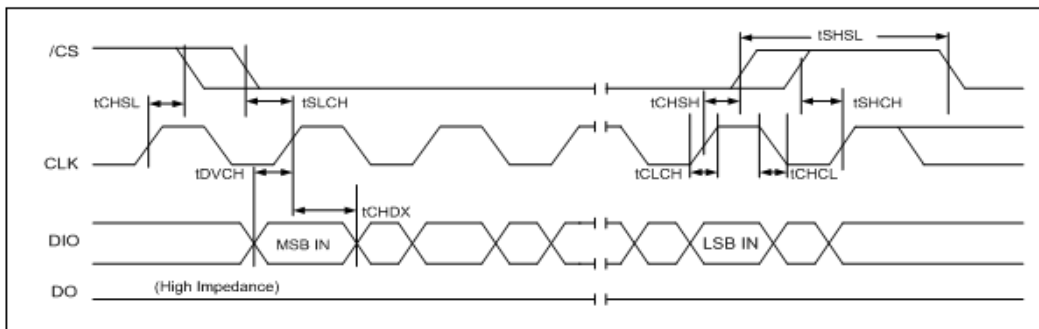
12.11 Hold Timing
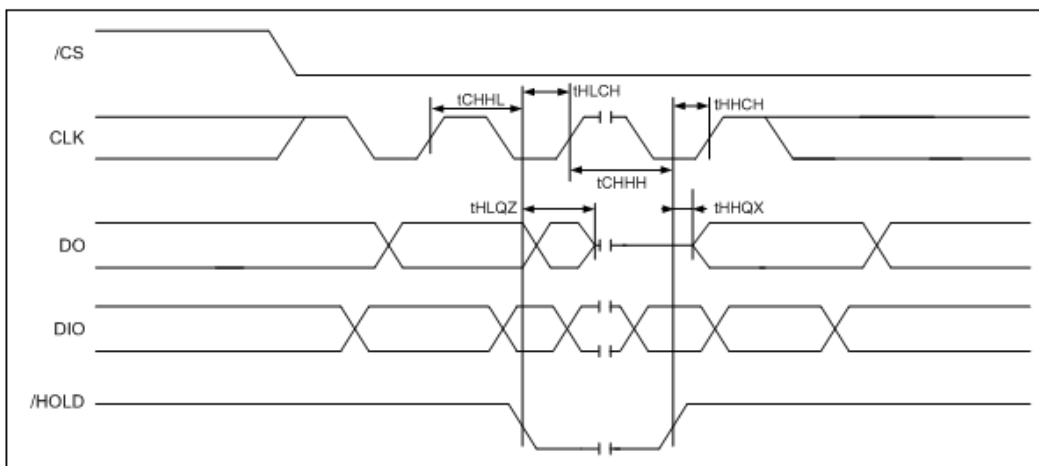
13. PACKAGE SPECIFICATION
13.1 8-Pin SOIC 208-mil
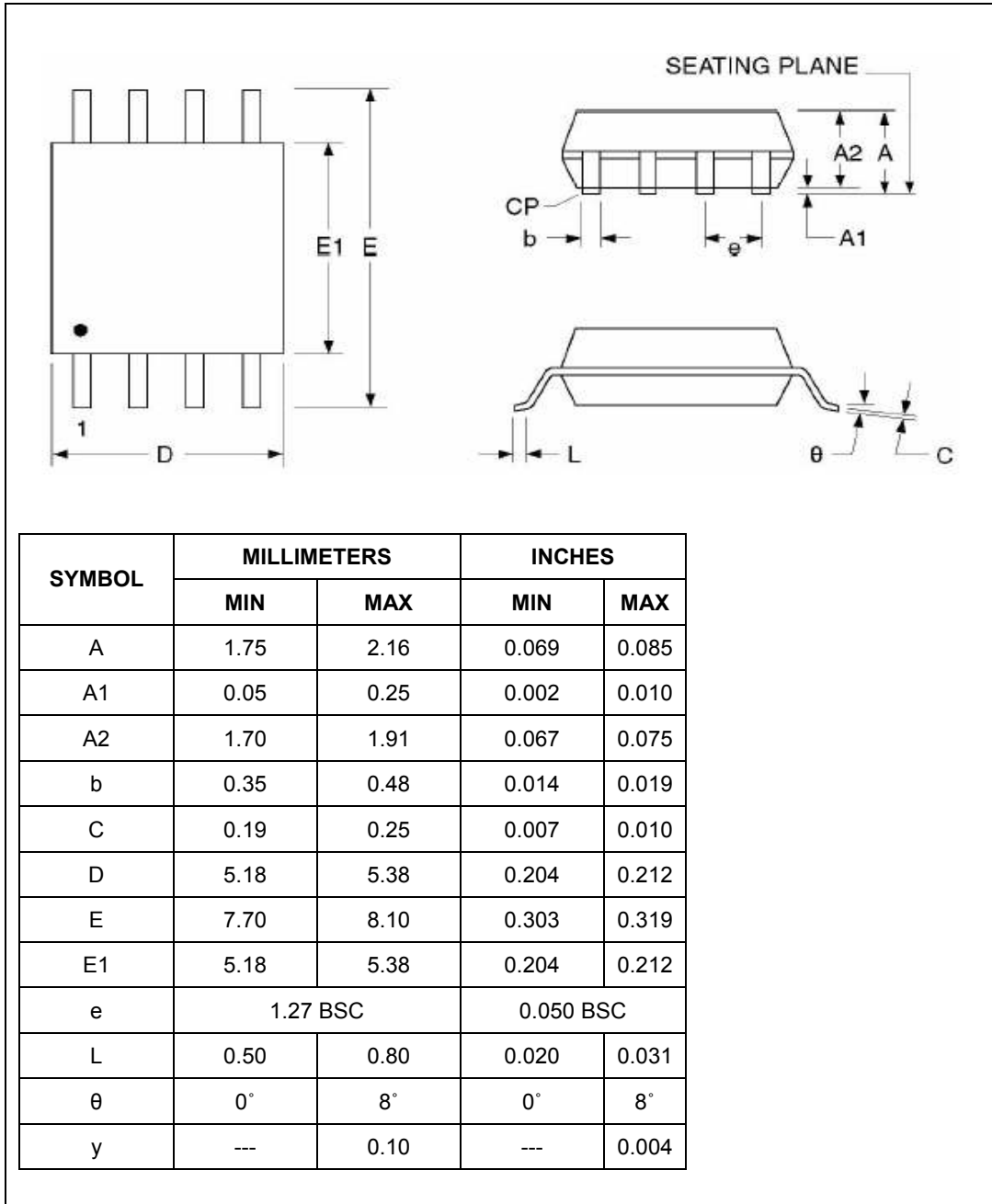
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.75	2.16	0.069	0.085
A1	0.05	0.25	0.002	0.010
A2	1.70	1.91	0.067	0.075
b	0.35	0.48	0.014	0.019
C	0.19	0.25	0.007	0.010
D	5.18	5.38	0.204	0.212
E	7.70	8.10	0.303	0.319
E1	5.18	5.38	0.204	0.212
e	1.27 BSC		0.050 BSC	
L	0.50	0.80	0.020	0.031
θ	0°	8°	0°	8°
y	---	0.10	---	0.004

Notes:

1. Controlling dimensions: inches, unless otherwise specified.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
4. Formed leads shall be planar with respect to one another within. 0004 inches at the seating plane.

13.2 8-Pin PDIP 300-mil

SYMBOL	Dimension in inch			Dimension in min		
	MIN	Nom	MAX	MIN	Nom	MAX
A	---	---	0.210	---	---	5.334
A_1	0.015	---	---	0.381	---	---
A_2	0.125	0.130	0.135	3.18	3.30	3.43
B	0.016	0.018	0.022	0.41	0.46	0.56
B_1	0.058	0.060	0.064	1.47	1.52	1.63
c	0.008	0.010	0.014	0.20	0.25	0.36
D	0.360	0.365	0.370	9.14	9.27	9.40
E	0.290	0.300	0.310	7.37	7.62	7.87
E_1	0.245	0.250	0.255	6.22	6.35	6.48
e_1	0.090	0.100	0.110	2.29	2.54	2.79
L	0.120	0.130	0.140	3.05	3.30	3.56
α	0	---	15	0	---	15
e A	0.335	0.355	0.375	8.51	9.02	9.53
S	---	---	0.045	---	---	1.14

13.3 8-contact 6x5 WSON

SYMBOL	MILLIMETERS			INCHES		
	MIN	TYP.	MAX	MIN	TYP.	MAX
A	0.70	0.75	0.80	0.0276	0.0295	0.0315
A1	0.00	0.02	0.05	0.0000	0.0008	0.0019
A2		0.55			0.0126	
A3	0.19	0.20	0.25	0.0075	0.0080	0.0098
b	0.36	0.40	0.48	0.0138	0.0157	0.0190
D[3]	5.90	6.00	6.10	0.2320	0.2360	0.2400
D1	3.30	3.40	3.50	0.1299	0.1338	0.1377
E	4.90	5.00	5.10	0.1930	0.1970	0.2010
E1[3]	4.20	4.30	4.40	0.1653	0.1692	0.1732
e[2]	1.27 BSC			0.0500 BSC		
K	0.20			0.0080		
L	0.50	0.60	0.75	0.0197	0.0236	0.0295

13.4 8-contact 6x5 WSON Cont'd.

RECOMMENDED SOLDER PATTERN
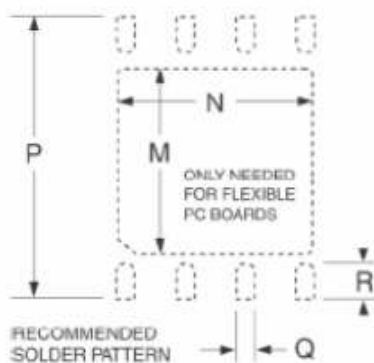
SYMBOL	MILLIMETERS			INCHES		
	MIN	TYP.	MAX	MIN	TYP.	MAX
SOLDER PATTERN						
M		3.40			0.1338	
N		4.30			0.1692	
P		6.00			0.2360	
Q		0.50			0.0196	
R		0.75			0.0255	

Notes:

1. Advanced Packaging Information; please contact FIDELIX SEMICONDUCTOR for the latest minimum and maximum specifications.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
4. The metal pad area on the bottom center of the package is connected to the device ground (GND pin). Avoid placement of exposed PCB bias under the pad.

13.5 16-Pin SOIC 300-mil
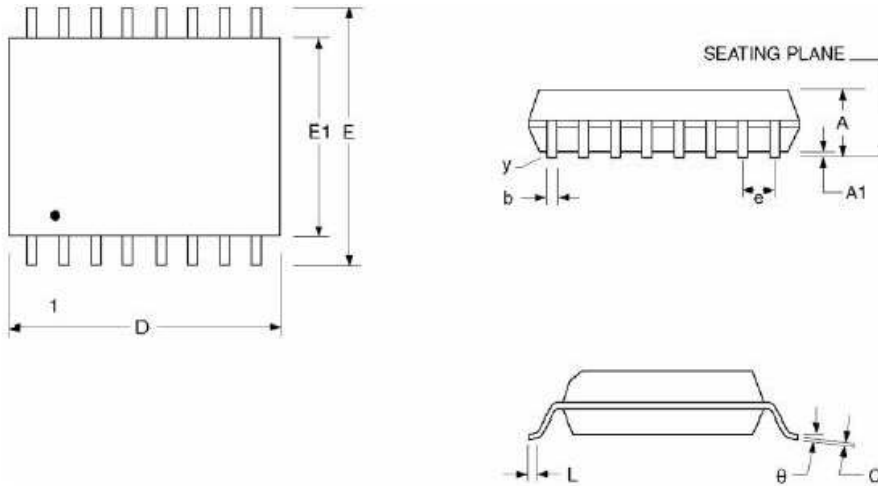
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.36	2.64	0.093	0.104
A1	0.10	0.30	0.005	0.012
b	0.33	0.51	0.013	0.020
C	0.18	0.28	0.007	0.000
D(3)	10.08	10.49	0.397	0.413
E	10.01	10.64	0.394	0.419
E1(3)	7.39	7.59	0.291	0.299
e(2)	1.27BSC		0.050	
L	0.39	1.27	0.015	0.050
θ	0°	8°	0°	8°
y	---	0.076	---	0.003

Notes:

1. Controlling dimensions: inches, unless otherwise specified.
2. BSC = Basic lead spacing between centers.
3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.

14. ORDERING INFORMATION[1]

FM XXXXX X - XXXX X X

Fidelix Memory

Product Family
25 : SPI

Organization
S : Standard
D : Dual
Q : Quad

Device Depth
04 : 4M
08 : 8M
16 : 16M
32 : 32M
64 : 64M
4A : 128M

Generation
A : 1st
B : 2nd
C : 3nd

Speed
85 : 85MHz
1A : 104MHz

Packing Type
T : Tube (Standard)
R : Tape and Reel
Y : Tray
* Package NO Marking

Business Package Type
1 : 8 Pin 208 mil SOIC
2 : 16 Pin 300 mil SOIC
3 : 8 Pin 300 mil PDIP
4 : 8 Contact 6x5 WSON
5 : 8 Pin 150 mil SOIC
6 : 8 Contact 6x8 WSON
W : Wafer

Core / IO Voltage
A : 3.0V / 3.0V
B : 1.8V / 1.8V

Temperature
I (Industrial)   : -40℃~85℃
C (Commercial) :   0℃~70℃